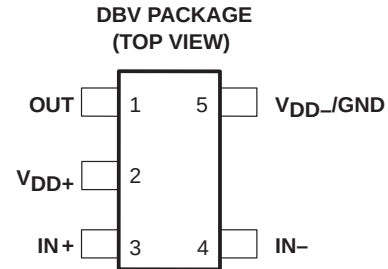


- Output Swing Includes Both Supply Rails
- Low Noise . . . 21 nV/√Hz Typ at f = 1 kHz
- Low Input Bias Current . . . 1 pA Typ
- Very Low Power . . . 11 μA Per Channel Typ
- Common-Mode Input Voltage Range Includes Negative Rail
- Wide Supply Voltage Range 2.7 V to 10 V
- Available in the SOT-23 Package
- Macromodel Included



description

The TLV2711 is a single low-voltage operational amplifier available in the SOT-23 package. It consumes only 11 μA (typ) of supply current and is ideal for battery-power applications. Looking at Figure 1, the TLV2711 has a 3-V noise level of 21 nV/√Hz at 1kHz; five times lower than competitive SOT-23 micropower solutions. The device exhibits rail-to-rail output performance for increased dynamic range in single- or split-supply applications. The TLV2711 is fully characterized at 3 V and 5 V and is optimized for low-voltage applications.

The TLV2711, exhibiting high input impedance and low noise, is excellent for small-signal conditioning for high-impedance sources, such as piezoelectric transducers. Because of the micropower dissipation levels combined with 3-V operation, these devices work well in hand-held monitoring and remote-sensing applications. In addition, the rail-to-rail output feature with single or split supplies makes this family a great choice when interfacing with analog-to-digital converters (ADCs).

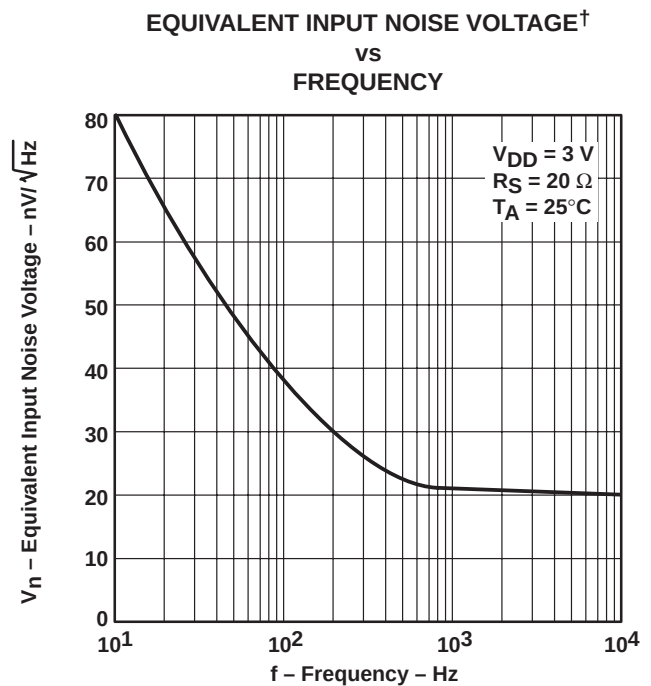


Figure 1. Equivalent Input Noise Voltage Versus Frequency

AVAILABLE OPTIONS

T _A	V _{IOmax} AT 25°C	PACKAGED DEVICES	SYMBOL	CHIP FORM [‡] (Y)
		SOT-23 (DBV) [†]		
0°C to 70°C	3 mV	TLV2711CDBV	VAJC	TLV2711Y
–40°C to 85°C	3 mV	TLV2711IDBV	VAJI	

[†] The DBV package available in tape and reel only.

[‡] Chip forms are tested at T_A = 25°C only.



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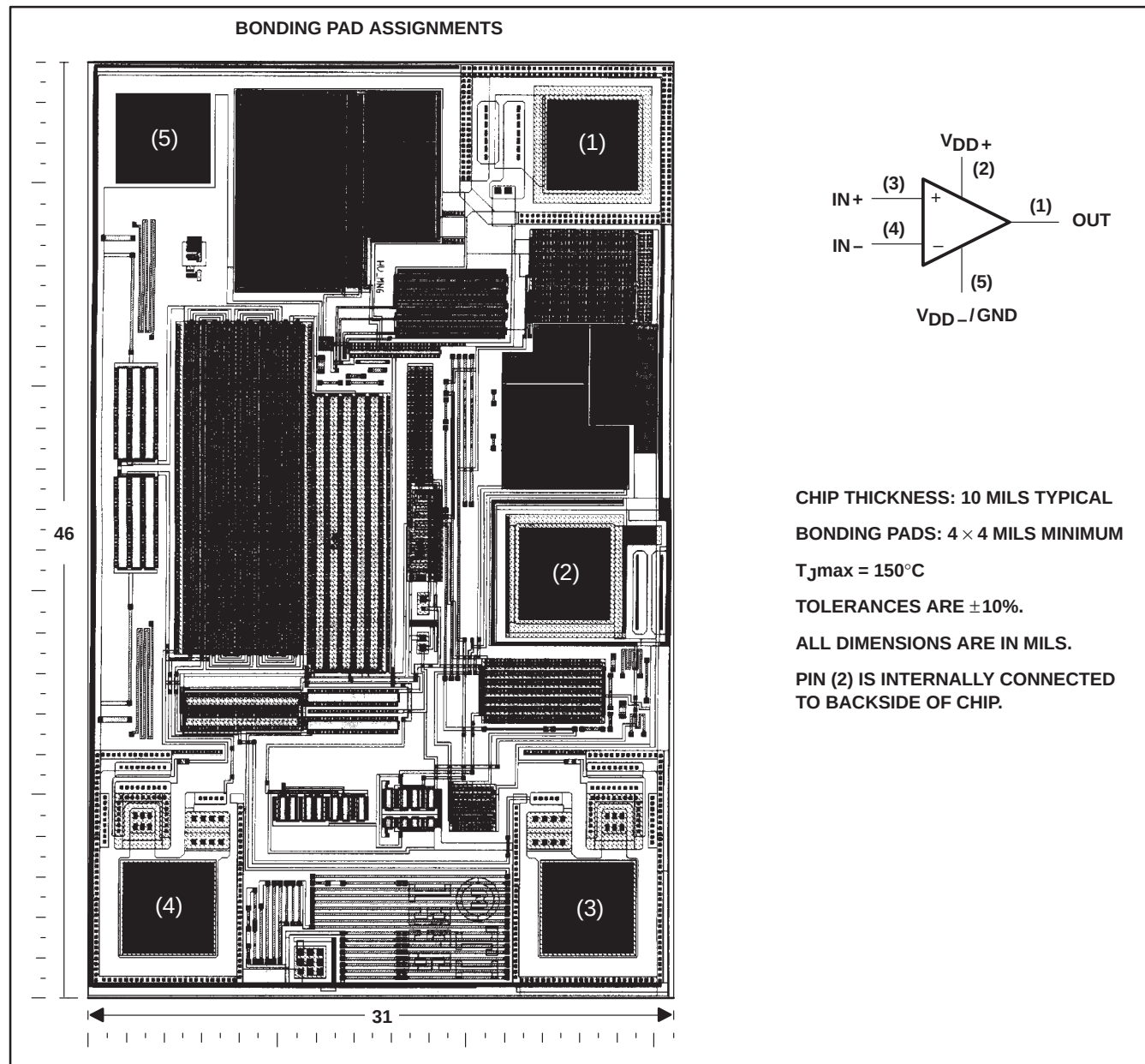
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description (continued)

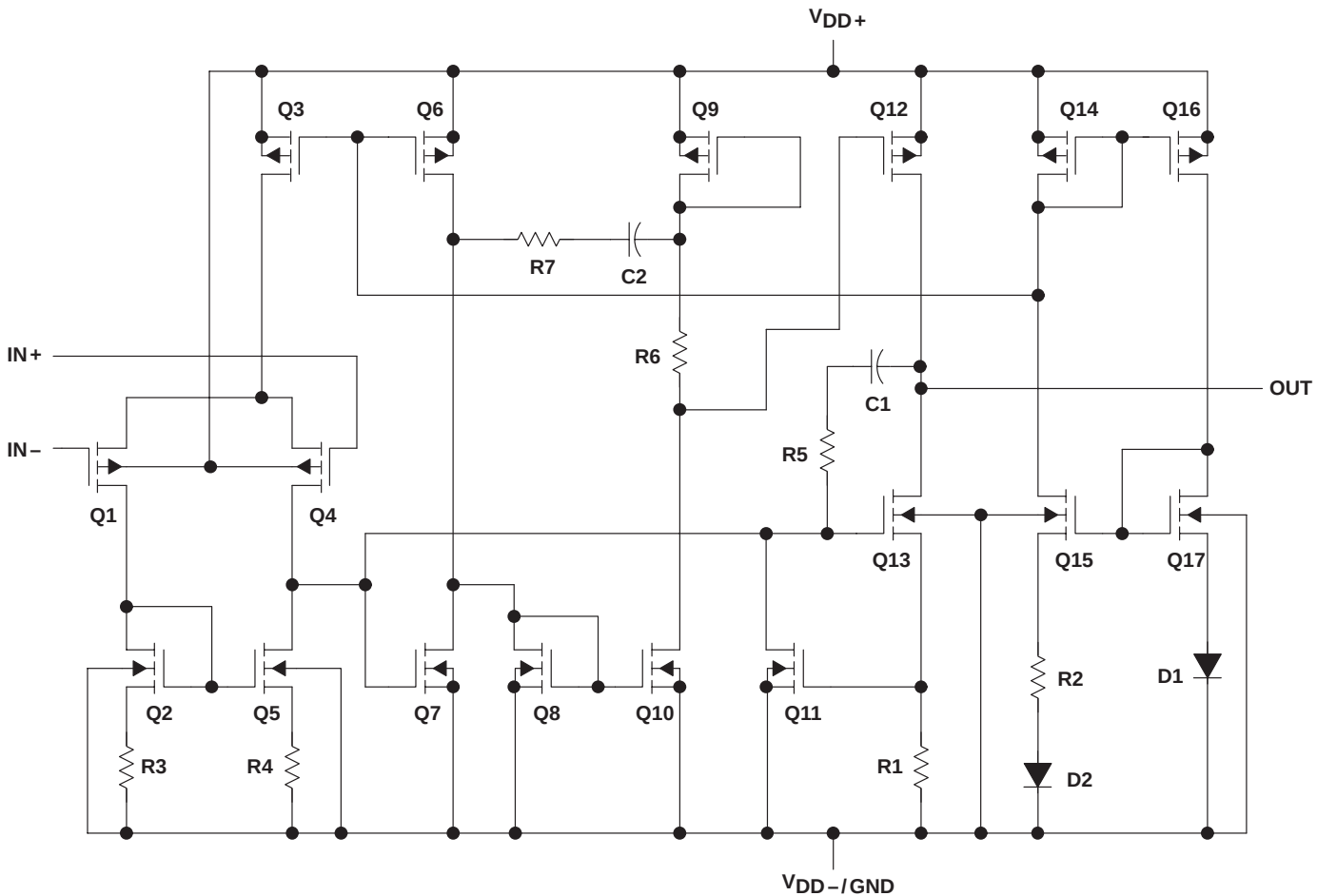
With a total area of 5.6mm², the SOT-23 package only requires one-third the board space of the standard 8-pin SOIC package. This ultra-small package allows designers to place single amplifiers very close to the signal source, minimizing noise pick-up from long PCB traces.

TLV2711Y chip information

This chip, when properly assembled, displays characteristics similar to the TLV2711C. Thermal compression or ultrasonic bonding may be used on the doped-aluminum bonding pads. This chip may be mounted with conductive epoxy or a gold-silicon preform.



equivalent schematic



COMPONENT COUNT†	
Transistors	23
Diodes	6
Resistors	11
Capacitors	2

† Includes both amplifiers and all ESD, bias, and trim circuitry

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absolute maximum ratings over operating free-air temperature range (unless otherwise noted)[†]

Supply voltage, V_{DD} (see Note 1)	12 V
Differential input voltage, V_{ID} (see Note 2)	$\pm V_{DD}$
Input voltage range, V_I (any input, see Note 1)	$-0.3\text{ V to }V_{DD}$
Input current, I_I (each input)	$\pm 5\text{ mA}$
Output current, I_O	$\pm 50\text{ mA}$
Total current into V_{DD+}	$\pm 50\text{ mA}$
Total current out of V_{DD-}	$\pm 50\text{ mA}$
Duration of short-circuit current (at or below) 25°C (see Note 3)	unlimited
Continuous total power dissipation	See Dissipation Rating Table
Operating free-air temperature range, T_A : TLV2711C	0°C to 70°C
TLV2711I	-40°C to 85°C
Storage temperature range, T_{stg}	-65°C to 150°C
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds: DBV package	260°C

[†] Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES:
1. All voltage values, except differential voltages, are with respect to V_{DD-} .
 2. Differential voltages are at the noninverting input with respect to the inverting input. Excessive current flows when input is brought below $V_{DD-} - 0.3\text{ V}$.
 3. The output may be shorted to either supply. Temperature and/or supply voltages must be limited to ensure that the maximum dissipation rating is not exceeded.

DISSIPATION RATING TABLE

PACKAGE	$T_A \leq 25^\circ\text{C}$ POWER RATING	DERATING FACTOR ABOVE $T_A = 25^\circ\text{C}$	$T_A = 70^\circ\text{C}$ POWER RATING	$T_A = 85^\circ\text{C}$ POWER RATING
DBV	150 mW	1.2 mW/°C	96 mW	78 mW

recommended operating conditions

	TLV2711C		TLV2711I		UNIT
	MIN	MAX	MIN	MAX	
Supply voltage, V_{DD} (see Note 1)	2.7	10	2.7	10	V
Input voltage range, V_I	V_{DD-}	$V_{DD+} - 1.3$	V_{DD-}	$V_{DD+} - 1.3$	V
Common-mode input voltage, V_{IC}	V_{DD-}	$V_{DD+} - 1.3$	V_{DD-}	$V_{DD+} - 1.3$	V
Operating free-air temperature, T_A	0	70	-40	85	°C

NOTE 1: All voltage values, except differential voltages, are with respect to V_{DD-} .



electrical characteristics at specified free-air temperature, $V_{DD} = 3\text{ V}$ (unless otherwise noted)

PARAMETER		TEST CONDITIONS		T _A [†]	TLV2711C			TLV2711I			UNIT
					MIN	TYP	MAX	MIN	TYP	MAX	
V _{IO}	Input offset voltage	V _{DD±} = ±1.5 V, V _O = 0, V _{IC} = 0, R _S = 50 Ω		Full range	0.4 3			0.4 3			mV
α _{VIO}	Temperature coefficient of input offset voltage				1			1			μV/°C
	Input offset voltage long-term drift (see Note 4)			25°C	0.003			0.003			μV/mo
I _{IO}	Input offset current			Full range	0.5 150			0.5 150			pA
I _{IB}	Input bias current			Full range	1 150			1 150			pA
V _{ICR}	Common-mode input voltage range	V _{IO} ≤5 mV, R _S = 50 Ω		25°C	0 –0.3 to to 2 2.2	0 –0.3 to to 2 2.2			V		
				Full range	0 to 1.7			0 to 1.7			
V _{OH}	High-level output voltage	I _{OH} = –100 μA		25°C	2.94			2.94			V
		I _{OH} = –250 μA		25°C	2.85			2.85			
				Full range	2.6			2.6			
V _{OL}	Low-level output voltage	V _{IC} = 1.5 V, I _{OL} = 50 μA		25°C	15			15			mV
		V _{IC} = 1.5 V, I _{OL} = 500 μA		25°C	150			150			
				Full range	500			500			
A _{VD}	Large-signal differential voltage amplification	V _{IC} = 1.5 V, V _O = 1 V to 2 V	R _L = 10 kΩ [‡]	25°C	3 7			3 7			V/mV
			R _L = 1 MΩ [‡]	Full range	1			1			
				25°C	600			600			
r _{i(d)}	Differential input resistance			25°C	10 ¹²			10 ¹²			Ω
r _{i(c)}	Common-mode input resistance			25°C	10 ¹²			10 ¹²			Ω
c _{i(c)}	Common-mode input capacitance	f = 10 kHz,		25°C	5			5			pF
z _o	Closed-loop output impedance	f = 7 kHz, A _V = 1		25°C	200			200			Ω
CMRR	Common-mode rejection ratio	V _{IC} = 0 to 1.7 V, R _S = 50 Ω	V _O = 1.5 V,	25°C	65 83	65 83			dB		
				Full range	60			60			
k _{SVR}	Supply voltage rejection ratio (ΔV _{DD} /ΔV _{IO})	V _{DD} = 2.7 V to 8 V, No load	V _{IC} = V _{DD} /2 ,	25°C	80 95	80 95			dB		
				Full range	80			80			
I _{DD}	Supply current	V _O = 1.5 V,	No load	25°C	11 25			11 25			μA
				Full range	30			30			

† Full range for the TLV2711C is 0°C to 70°C. Full range for the TLV2711I is –40°C to 85°C.

‡ Referenced to 1.5 V

NOTE 4: Typical values are based on the input offset voltage shift observed through 500 hours of operating life test at $T_A = 150^\circ\text{C}$ extrapolated to $T_A = 25^\circ\text{C}$ using the Arrhenius equation and assuming an activation energy of 0.96 eV.

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operating characteristics at specified free-air temperature, $V_{DD} = 3\text{ V}$ (unless otherwise noted)

PARAMETER		TEST CONDITIONS		T _A [†]	TLV2711C			TLV2711I			UNIT
					MIN	TYP	MAX	MIN	TYP	MAX	
SR	Slew rate at unity gain	V _O = 1.1 V to 1.9 V, R _L = 10 kΩ [‡] , C _L = 100 pF [‡]		25°C	0.01	0.025		0.01	0.025		V/μs
				Full range	0.005			0.005			
V _n	Equivalent input noise voltage	f = 10 Hz		25°C	80			80			nV/√Hz
		f = 1 kHz		25°C	22			22			
V _{N(PP)}	Peak-to-peak equivalent input noise voltage	f = 0.1 Hz to 1 Hz		25°C	660			660			μV
		f = 0.1 Hz to 10 Hz		25°C	880			880			
I _n	Equivalent input noise current			25°C	0.6			0.6			fA/√Hz
Gain-bandwidth product		f = 10 kHz, R _L = 10 kΩ [‡] , C _L = 100 pF [‡]		25°C	56			56			kHz
B _{OM}	Maximum output-swing bandwidth	V _{O(PP)} = 1 V, R _L = 10 kΩ [‡] ,	A _V = 1, C _L = 100 pF [‡]	25°C	7			7			kHz
φ _m	Phase margin at unity gain	R _L = 10 kΩ [‡] , C _L = 100 pF [‡]		25°C	56°			56°			
Gain margin				25°C	20			20			dB

† Full range is -40°C to 85°C .

‡ Referenced to 1.5 V

electrical characteristics at specified free-air temperature, $V_{DD} = 5\text{ V}$ (unless otherwise noted)

PARAMETER		TEST CONDITIONS		T _A [†]	TLV2711C			TLV2711I			UNIT
					MIN	TYP	MAX	MIN	TYP	MAX	
V _{IO}	Input offset voltage	V _{DD±} = ±2.5 V, V _O = 0, V _{IC} = 0, R _S = 50 Ω		Full range	0.45 3			0.45 3			mV
α _{VIO}	Temperature coefficient of input offset voltage				0.5			0.5			μV/°C
	Input offset voltage long-term drift (see Note 4)			25°C	0.003			0.003			μV/mo
I _{IO}	Input offset current			25°C	0.5			0.5			pA
I _{IB}	Input bias current			Full range	150			150			
				25°C	1			1			pA
		Full range	150			150					
V _{ICR}	Common-mode input voltage range	V _{IO} ≤5 mV R _S = 50 Ω		25°C	0 to 4	−0.3 to 4.2		0 to 4	−0.3 to 4.2		V
				Full range	0 to 3.5			0 to 3.5			
V _{OH}	High-level output voltage	I _{OH} = −100 μA		25°C	4.95			4.95			V
		I _{OH} = −250 μA		25°C	4.875			4.875			
				Full range	4.6			4.6			
V _{OL}	Low-level output voltage	V _{IC} = 2.5 V, I _{OL} = 50 μA		25°C	12			12			mV
		V _{IC} = 2.5 V, I _{OL} = 500 μA		25°C	120			120			
				Full range	500			500			
A _{VD}	Large-signal differential voltage amplification	V _{IC} = 2.5 V, V _O = 1 V to 4 V	R _L = 10 kΩ [‡]	25°C	6	12		6	12		V/mV
			R _L = 1 MΩ [‡]	Full range	3			3			
				25°C	800			800			
r _{i(d)}	Differential input resistance			25°C	10 ¹²			10 ¹²			Ω
r _{i(c)}	Common-mode input resistance			25°C	10 ¹²			10 ¹²			Ω
c _{i(c)}	Common-mode input capacitance	f = 10 kHz,		25°C	5			5			pF
z _o	Closed-loop output impedance	f = 7 kHz, A _V = 1		25°C	200			200			Ω
CMRR	Common-mode rejection ratio	V _{IC} = 0 to 2.7 V, R _S = 50 Ω, V _O = 2.5 V		25°C	70	83		70	83		dB
				Full range	70			70			
k _{SVR}	Supply voltage rejection ratio (ΔV _{DD} /ΔV _{IO})	V _{DD} = 4.4 V to 8 V, No load, V _{IC} = V _{DD} /2,		25°C	80	95		80	95		dB
				Full range	80			80			
I _{DD}	Supply current	V _O = 2.5 V, No load		25°C	13	25		13	25		μA
				Full range	30			30			

† Full range for the TLV2711C is 0°C to 70°C. Full range for the TLV2711I is –40°C to 85°C.

‡ Referenced to 1.5 V

NOTE 5: Typical values are based on the input offset voltage shift observed through 500 hours of operating life test at $T_A = 150^\circ\text{C}$ extrapolated to $T_A = 25^\circ\text{C}$ using the Arrhenius equation and assuming an activation energy of 0.96 eV.

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operating characteristics at specified free-air temperature, $V_{DD} = 5\text{ V}$ (unless otherwise noted)

PARAMETER		TEST CONDITIONS		T _A [†]	TLV2711C			TLV2711I			UNIT
					MIN	TYP	MAX	MIN	TYP	MAX	
SR	Slew rate at unity gain	V _O = 1.5 V to 3.5 V, R _L = 10 kΩ [‡] , C _L = 100 pF [‡]		25°C	0.01	0.025		0.01	0.025		V/μs
				Full range	0.005			0.005			
V _n	Equivalent input noise voltage	f = 10 Hz		25°C	72			72			nV/√Hz
		f = 1 kHz		25°C	21			21			
V _{N(PP)}	Peak-to-peak equivalent input noise voltage	f = 0.1 Hz to 1 Hz		25°C	600			600			μV
		f = 0.1 Hz to 10 Hz		25°C	800			800			
I _n	Equivalent input noise current			25°C	0.6			0.6			fA/√Hz
Gain-bandwidth product		f = 10 kHz, R _L = 10 kΩ [‡] , C _L = 100 pF [‡]		25°C	65			65			kHz
B _{OM}	Maximum output-swing bandwidth	V _{O(PP)} = 2 V, A _V = 1, R _L = 10 kΩ [‡] , C _L = 100 pF [‡]		25°C	7			7			kHz
φ _m	Phase margin at unity gain	R _L = 10 kΩ [‡] , C _L = 100 pF [‡]		25°C	60°			60°			
Gain margin				25°C	22			22			dB

† Full range is -40°C to 85°C .

‡ Referenced to 1.5 V

electrical characteristics at $V_{DD} = 3\text{ V}, T_A = 25^\circ\text{C}$ (unless otherwise noted)

PARAMETER		TEST CONDITIONS			TLV2711Y			UNIT
					MIN	TYP	MAX	
V _{IO}	Input offset voltage	V _{DD±} = ±1.5 V, V _O = 0, V _{IC} = 0, R _S = 50 Ω			0.47			mV
I _{IO}	Input offset current				0.5			pA
I _{IB}	Input bias current				1			pA
V _{ICR}	Common-mode input voltage range	V _{IO} ≤ 5 mV, R _S = 50 Ω			−0.3 to 2.2			V
V _{OH}	High-level output voltage	I _{OH} = −100 μA			2.94			V
		I _{OH} = −200 μA			2.85			
V _{OL}	Low-level output voltage	V _{IC} = 0, I _{OL} = 50 μA			15			mV
		V _{IC} = 0, I _{OL} = 500 μA			150			
A _{VD}	Large-signal differential voltage amplification	V _{IC} = 1.5 V, V _O = 1 V to 2 V	R _L = 10 kΩ†		7			V/mV
			R _L = 1 MΩ†		600			
r _{i(d)}	Differential input resistance				10 ¹²			Ω
r _{i(c)}	Common-mode input resistance				10 ¹²			Ω
c _{i(c)}	Common-mode input capacitance	f = 10 kHz			5			pF
z _o	Closed-loop output impedance	f = 7 kHz, A _V = 1			200			Ω
CMRR	Common-mode rejection ratio	V _{IC} = 0 to 1.7 V, V _O = 1.5 V, R _S = 50 Ω			83			dB
k _{SVR}	Supply voltage rejection ratio (ΔV _{DD} /ΔV _{IO})	V _{DD} = 2.7 V to 8 V, V _{IC} = V _{DD} /2, No load			95			dB
I _{DD}	Supply current	V _O = 1.5 V, No load			11			μA

† Referenced to 1.5 V



electrical characteristics at $V_{DD} = 5\text{ V}$, $T_A = 25^\circ\text{C}$ (unless otherwise noted)

PARAMETER		TEST CONDITIONS			TLV2711Y			UNIT
					MIN	TYP	MAX	
V _{IO}	Input offset voltage	V _{DD} ± = ±2.5 V, V _{IC} = 0, V _O = 0, R _S = 50 Ω			0.45			mV
I _{IO}	Input offset current				0.5			pA
I _{IB}	Input bias current				1			pA
V _{ICR}	Common-mode input voltage range	V _{IO} ≤5 mV, R _S = 50 Ω			−0.3 to 4.2			V
V _{OH}	High-level output voltage	I _{OH} = −100 μA			4.95			V
		I _{OH} = −250 μA			4.875			
V _{OL}	Low-level output voltage	V _{IC} = 2.5 V, I _{OL} = 50 μA		12			mV	
		V _{IC} = 2.5 V, I _{OL} = 500 μA		120				
A _{VD}	Large-signal differential voltage amplification	V _{IC} = 2.5 V, V _O = 1 V to 4 V		R _L = 10 kΩ†	12			V/mV
				R _L = 1 MΩ†	800			
r _{i(d)}	Differential input resistance				10 ¹²			Ω
r _{i(c)}	Common-mode input resistance				10 ¹²			Ω
c _{i(c)}	Common-mode input capacitance	f = 10 kHz			5			pF
z _o	Closed-loop output impedance	f = 7 kHz, A _V = 1		200			Ω	
CMRR	Common-mode rejection ratio	V _{IC} = 0 to 2.7 V, V _O = 2.5 V, R _S = 50 Ω		83			dB	
k _{SVR}	Supply voltage rejection ratio (ΔV _{DD} /ΔV _{IO})	V _{DD} = 4.4 V to 8 V, V _{IC} = V _{DD} /2, No load		95			dB	
I _{DD}	Supply current	V _O = 2.5 V, No load		13			μA	

[†] Referenced to 1.5 V

TYPICAL CHARACTERISTICS

Table of Graphs

			FIGURE
V_{IO}	Input offset voltage	Distribution vs Common-mode input voltage	3, 4 5, 6
αV_{IO}	Input offset voltage temperature coefficient	Distribution	7, 8
I_{IB}/I_{IO}	Input bias and input offset currents	vs Free-air temperature	9
V_I	Input voltage	vs Supply voltage vs Free-air temperature	10 11
V_{OH}	High-level output voltage	vs High-level output current	12, 15
V_{OL}	Low-level output voltage	vs Low-level output current	13, 14, 16
$V_{O(PP)}$	Maximum peak-to-peak output voltage	vs Frequency	17
I_{OS}	Short-circuit output current	vs Supply voltage vs Free-air temperature	18 19
V_O	Output voltage	vs Differential input voltage	20, 21
A_{VD}	Differential voltage amplification	vs Load resistance vs Frequency vs Free-air temperature	22 23, 24 25, 26
z_o	Output impedance	vs Frequency	27, 28
CMRR	Common-mode rejection ratio	vs Frequency vs Free-air temperature	29 30
k_{SVR}	Supply-voltage rejection ratio	vs Frequency vs Free-air temperature	31, 32 33
I_{DD}	Supply current	vs Supply voltage	34
SR	Slew rate	vs Load capacitance vs Free-air temperature	35 36
V_O	Large-signal pulse response	vs Time	37, 38, 39, 40
V_O	Small-signal pulse response	vs Time	41, 42, 43, 44
V_n	Equivalent input noise voltage	vs Frequency	45, 46
	Noise voltage (referred to input)	Over a 10-second period	47
THD + N	Total harmonic distortion plus noise	vs Frequency	48
	Gain-bandwidth product	vs Free-air temperature vs Supply voltage	49 50
ϕ_m	Phase margin	vs Frequency vs Load capacitance	23, 24 51
	Gain margin	vs Load capacitance	52
B_1	Unity-gain bandwidth	vs Load capacitance	53

TYPICAL CHARACTERISTICS

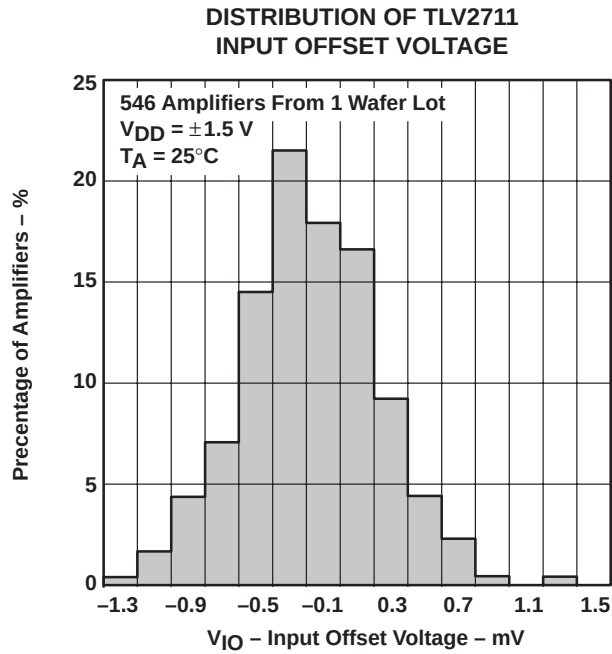


Figure 2

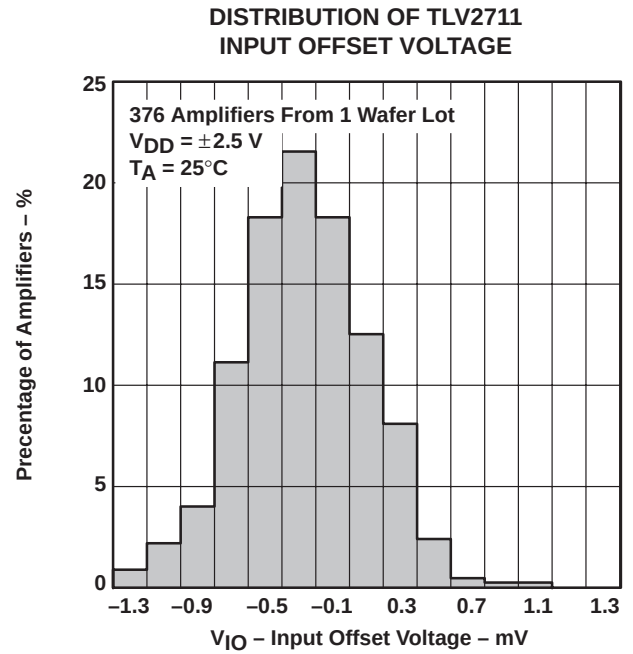


Figure 3

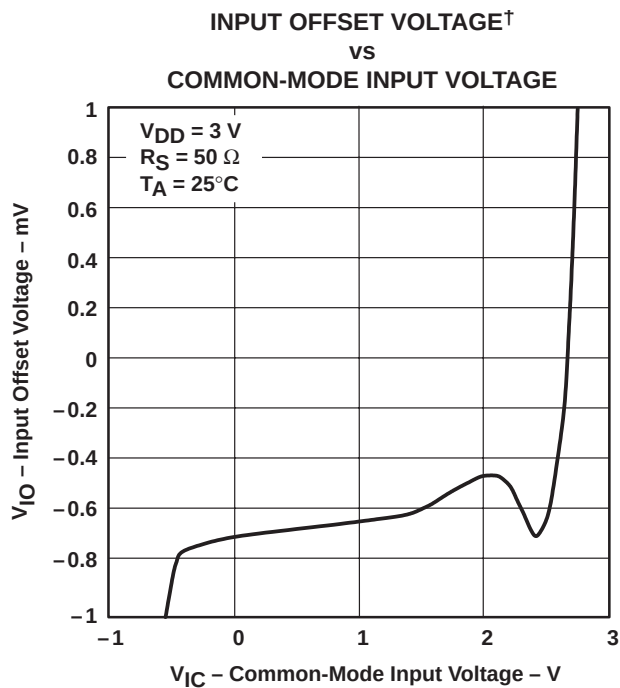


Figure 4

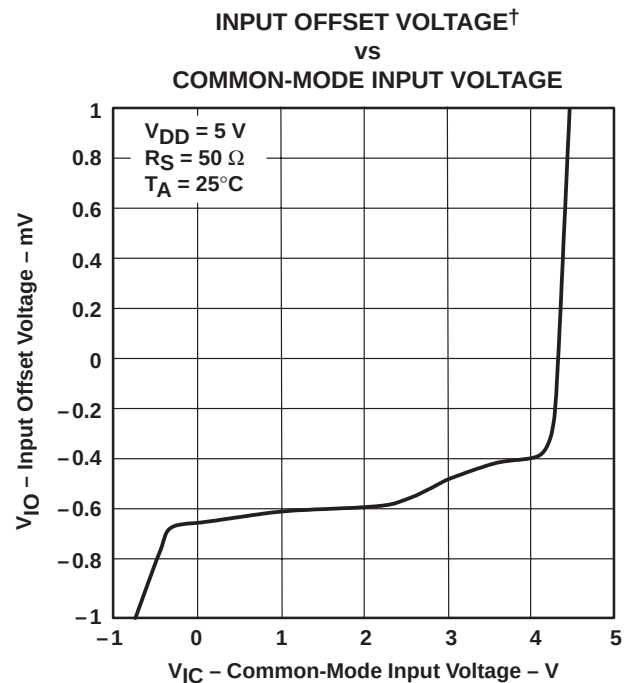


Figure 5

† For all curves where $V_{DD} = 5 \text{ V}$, all loads are referenced to 2.5 V. For all curves where $V_{DD} = 3 \text{ V}$, all loads are referenced to 1.5 V.

TYPICAL CHARACTERISTICS

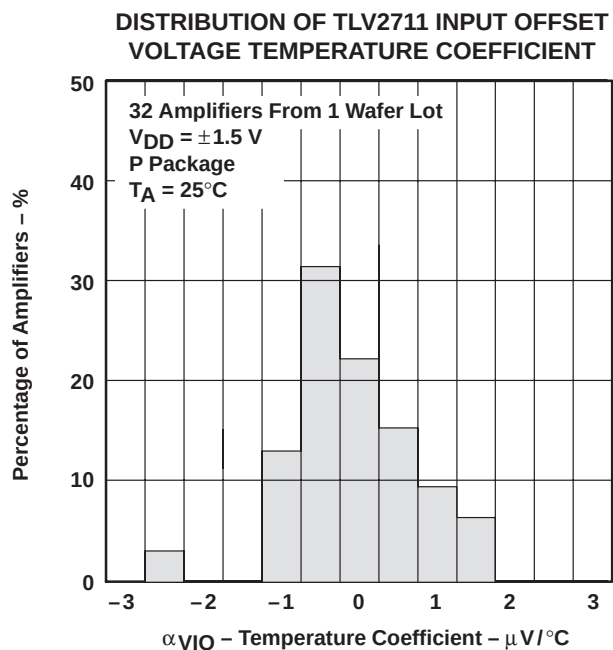


Figure 6

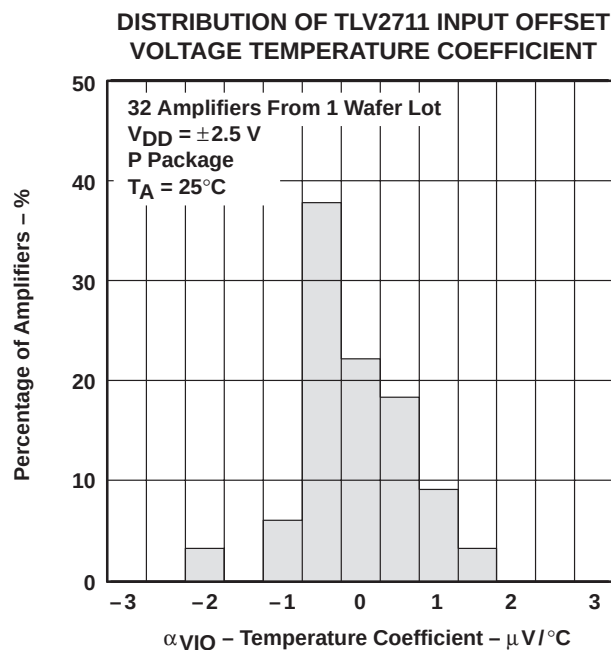


Figure 7

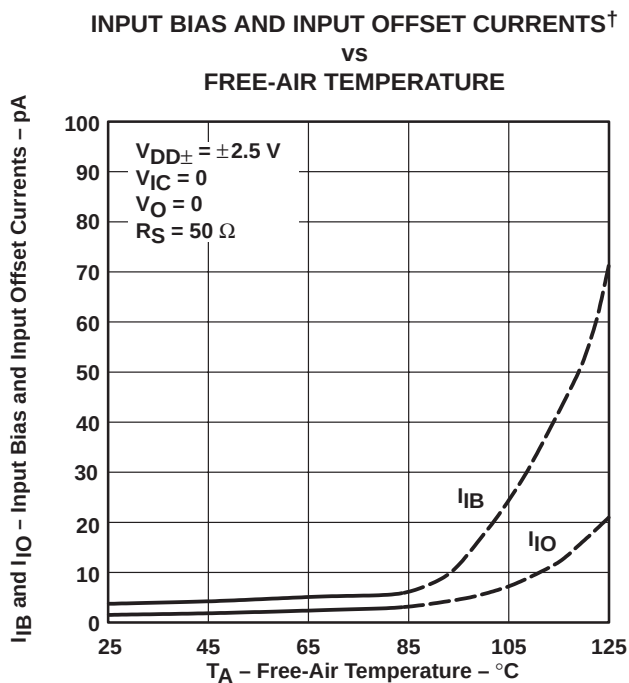


Figure 8

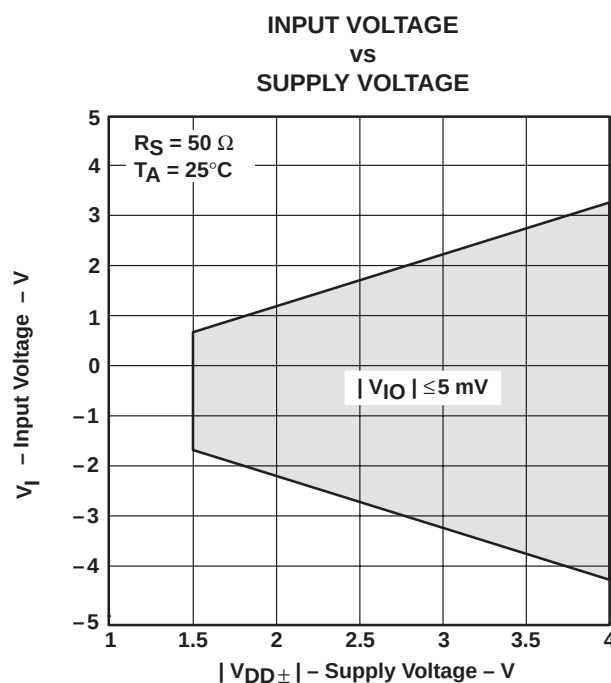
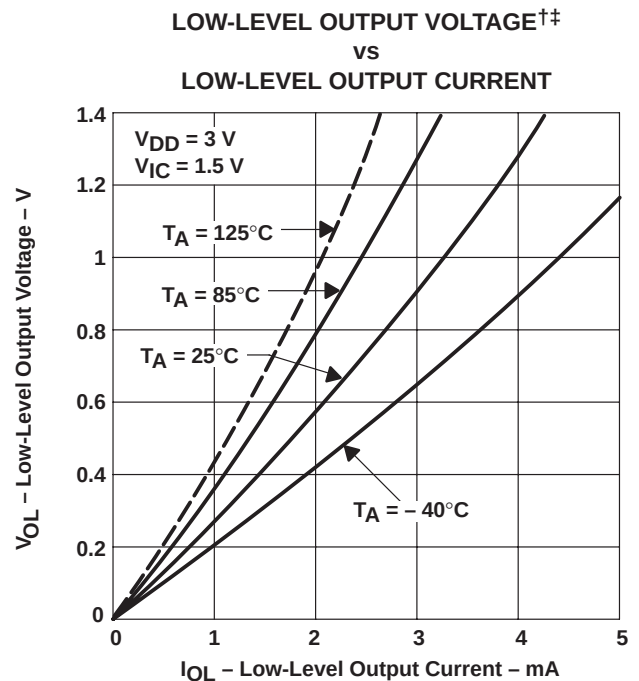
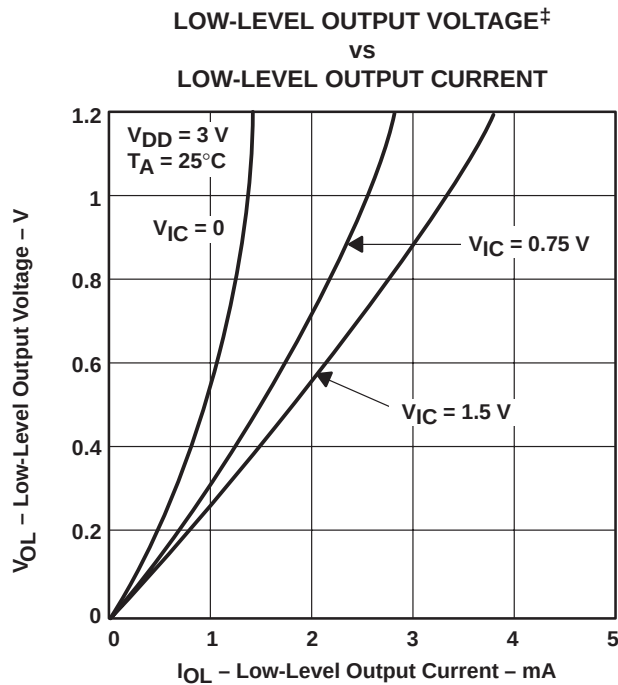
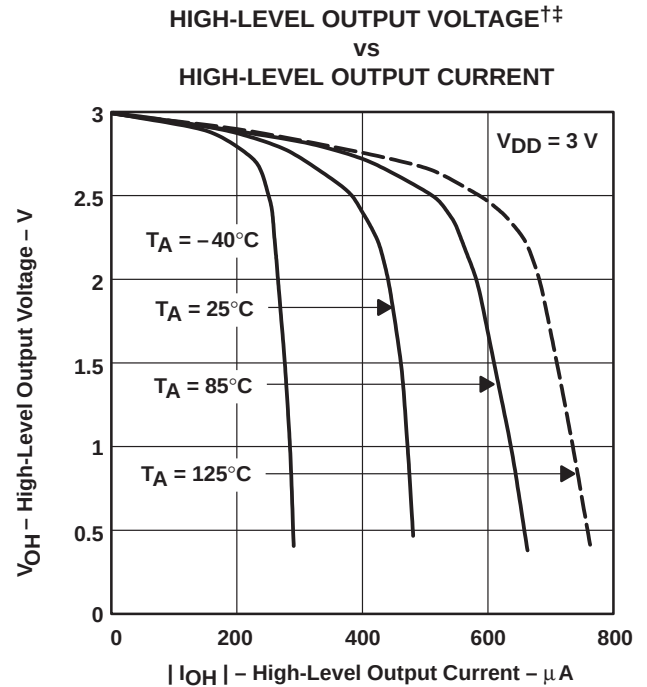
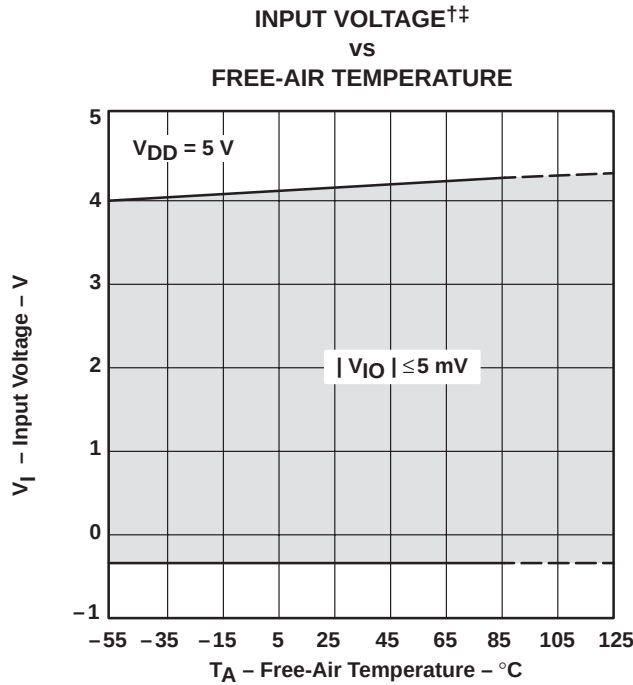


Figure 9

† Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.

TYPICAL CHARACTERISTICS



[†] Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.

[‡] For all curves where $V_{DD} = 5$ V, all loads are referenced to 2.5 V. For all curves where $V_{DD} = 3$ V, all loads are referenced to 1.5 V.

TYPICAL CHARACTERISTICS

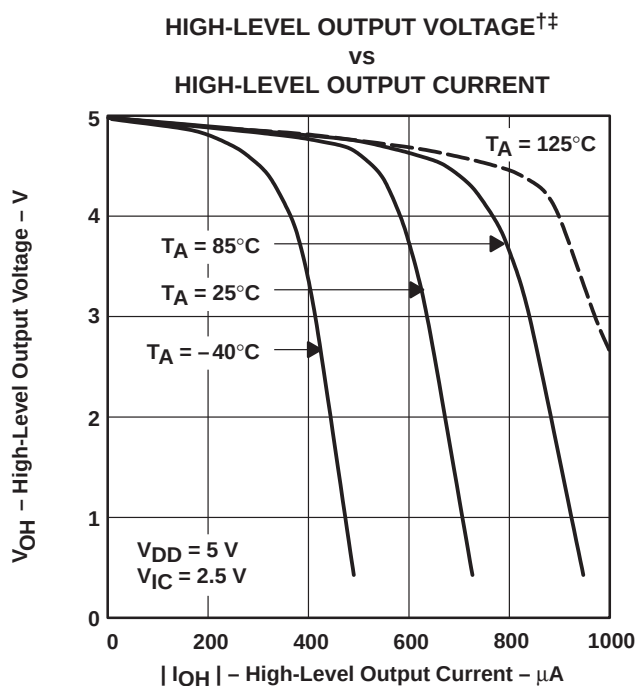


Figure 14

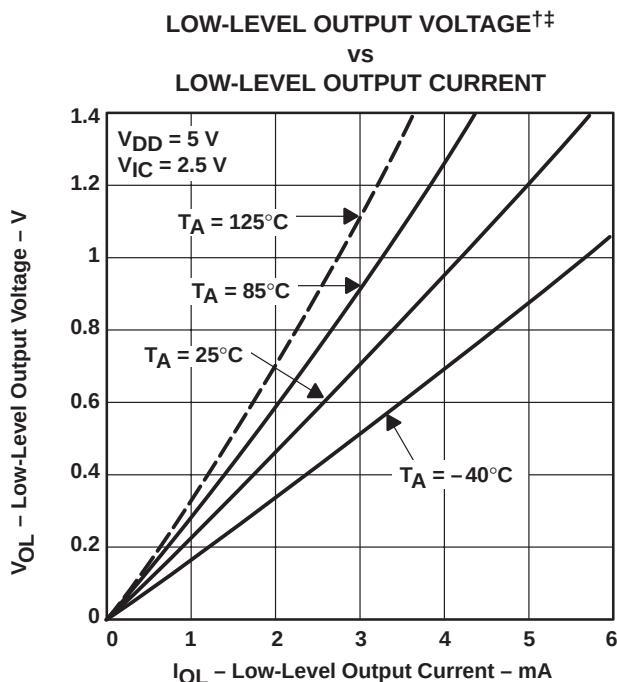


Figure 15

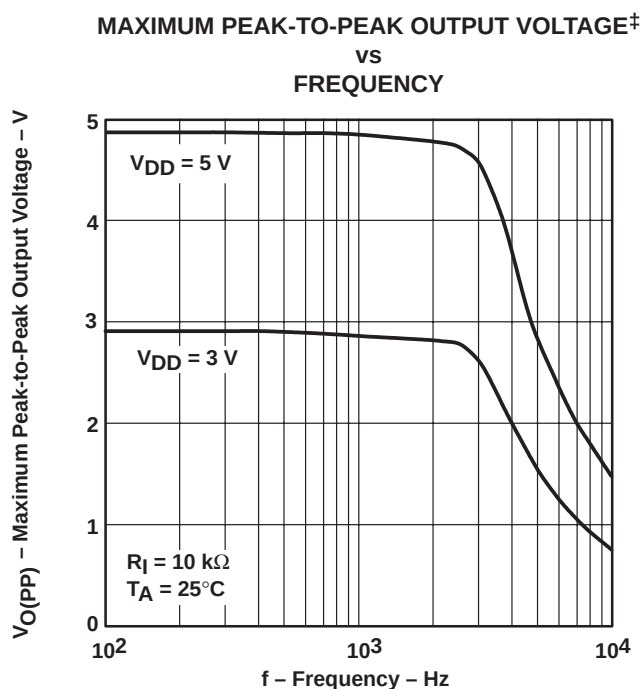


Figure 16

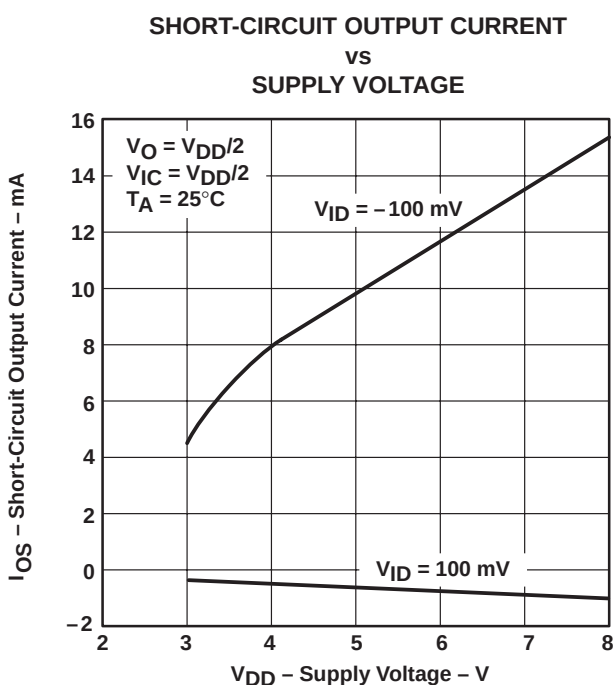


Figure 17

[†] Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.

[‡] For all curves where $V_{DD} = 5 V$, all loads are referenced to 2.5 V. For all curves where $V_{DD} = 3 V$, all loads are referenced to 1.5 V.

TYPICAL CHARACTERISTICS

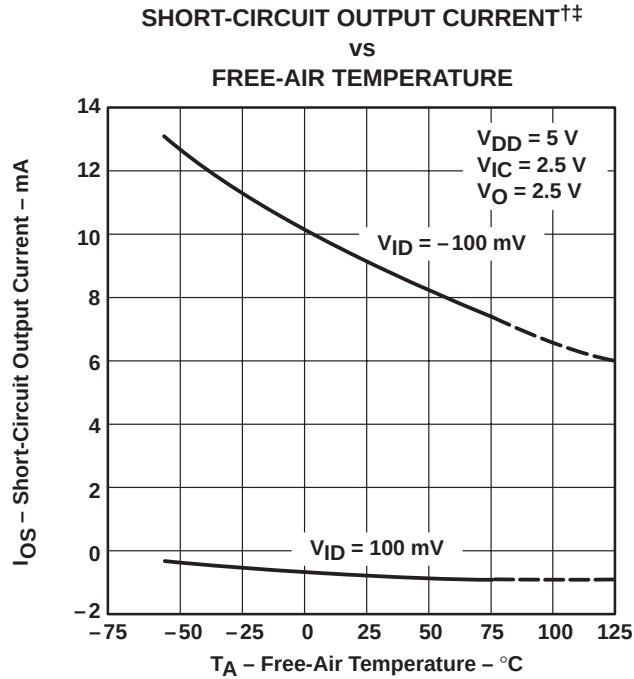


Figure 18

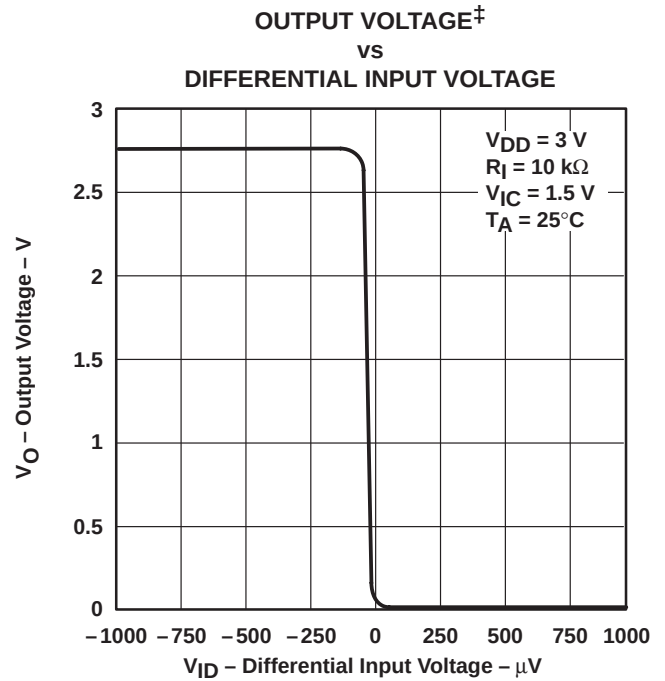


Figure 19

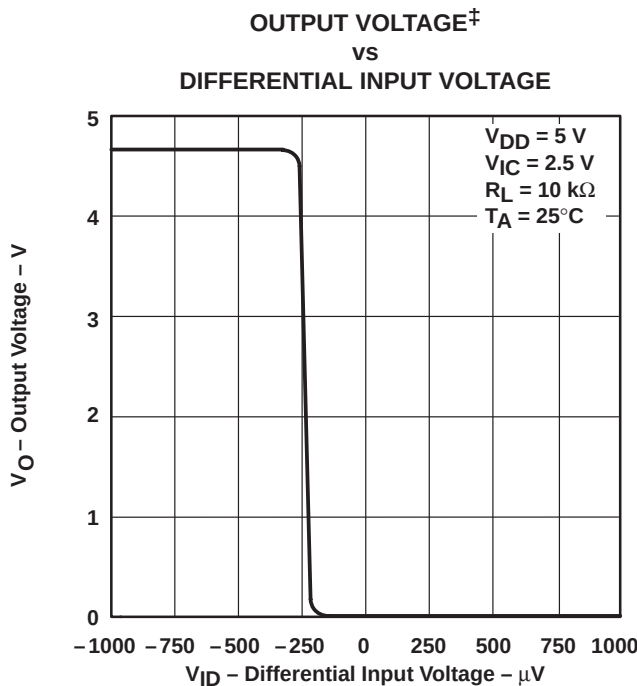


Figure 20

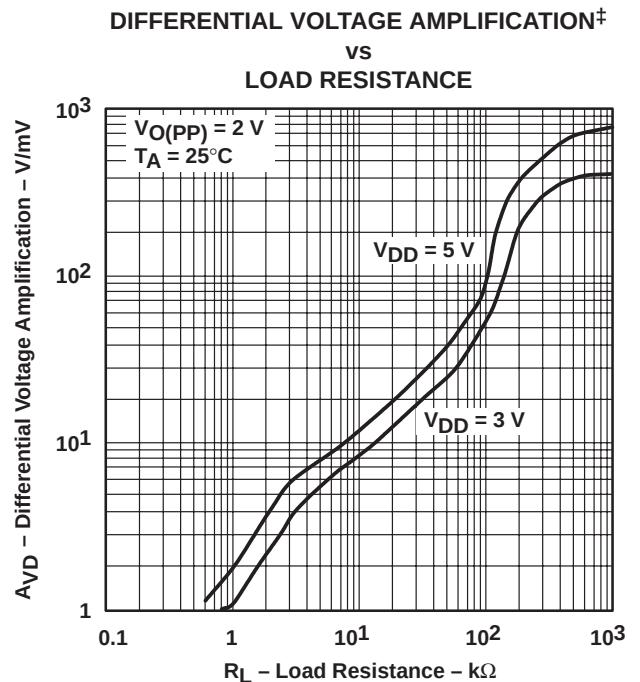


Figure 21

† Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.

‡ For all curves where $V_{DD} = 5\text{ V}$, all loads are referenced to 2.5 V. For all curves where $V_{DD} = 3\text{ V}$, all loads are referenced to 1.5 V.

TYPICAL CHARACTERISTICS

LARGE-SIGNAL DIFFERENTIAL VOLTAGE AMPLIFICATION AND PHASE MARGIN†

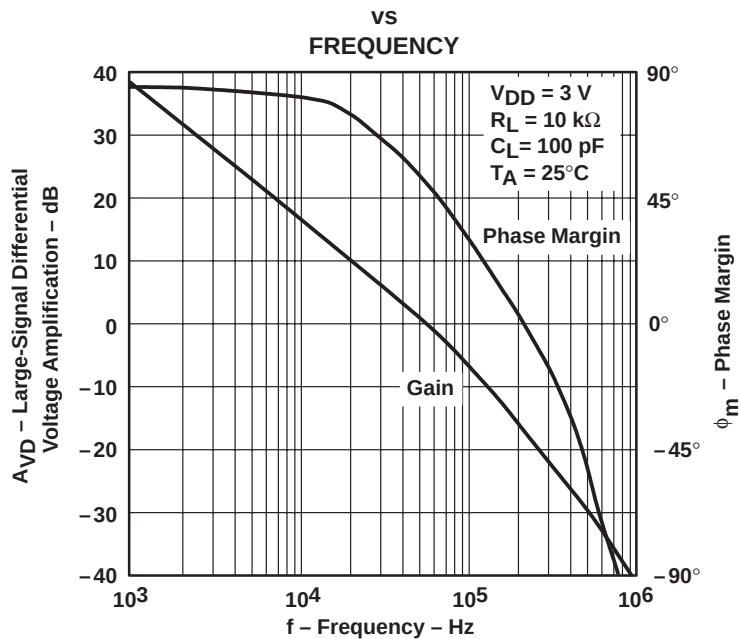


Figure 22

LARGE-SIGNAL DIFFERENTIAL VOLTAGE AMPLIFICATION AND PHASE MARGIN†

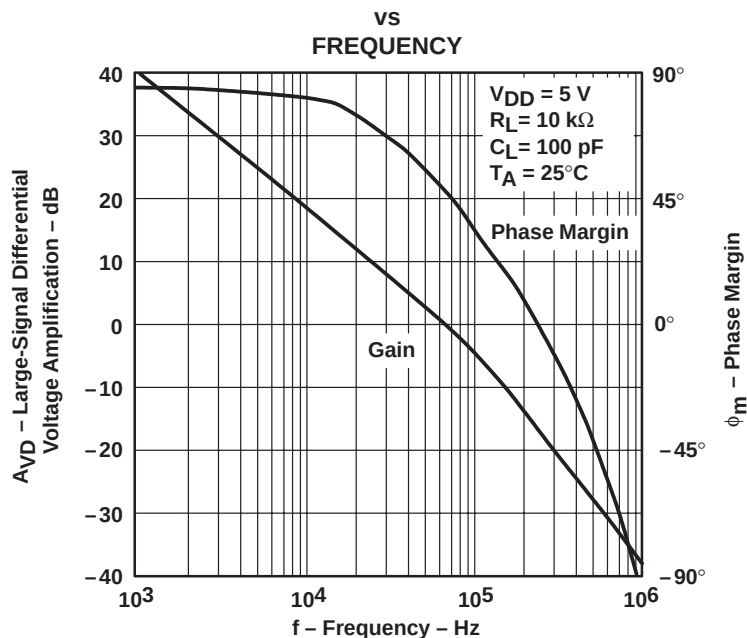


Figure 23

† For all curves where $V_{DD} = 5\text{ V}$, all loads are referenced to 2.5 V. For all curves where $V_{DD} = 3\text{ V}$, all loads are referenced to 1.5 V.

TYPICAL CHARACTERISTICS

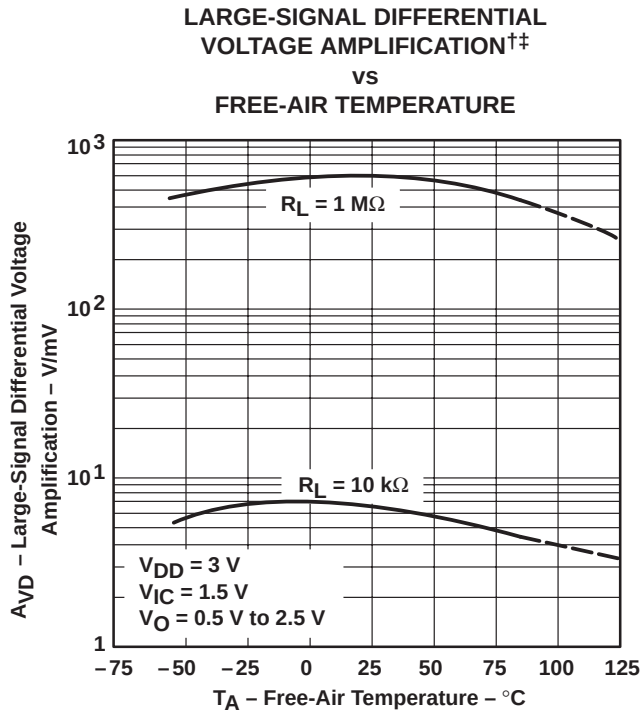


Figure 24

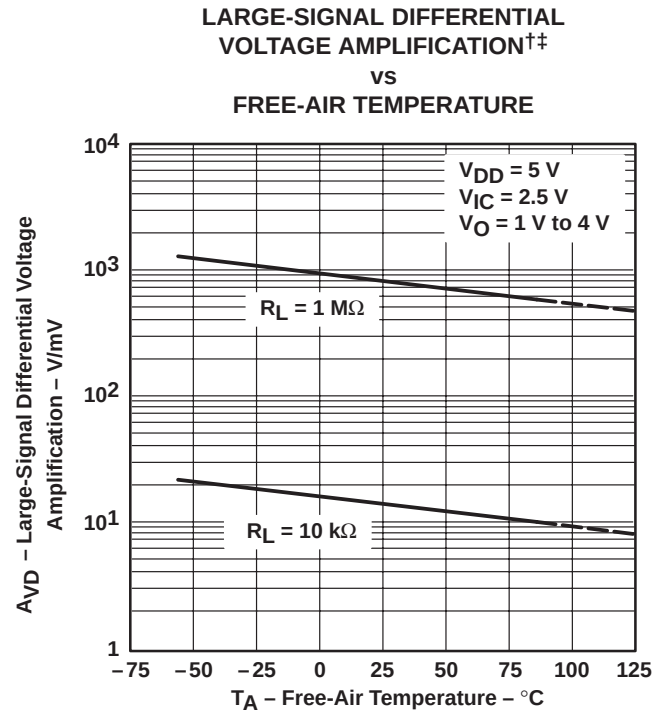


Figure 25

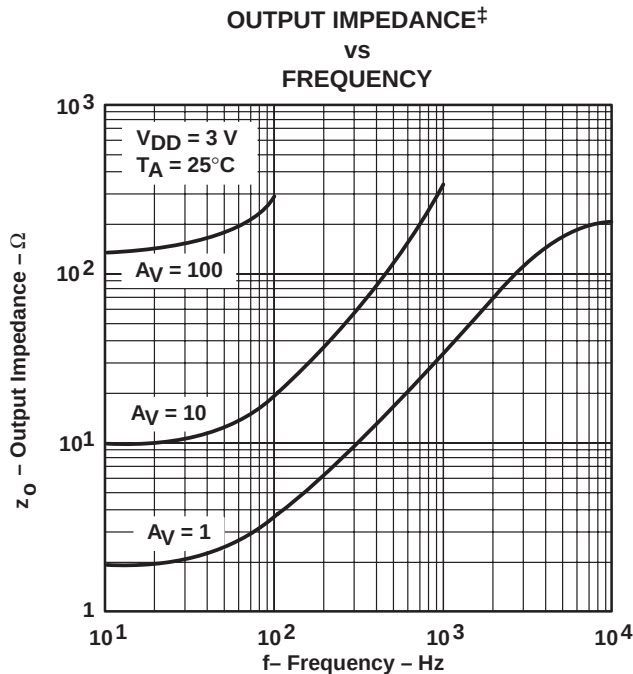


Figure 26

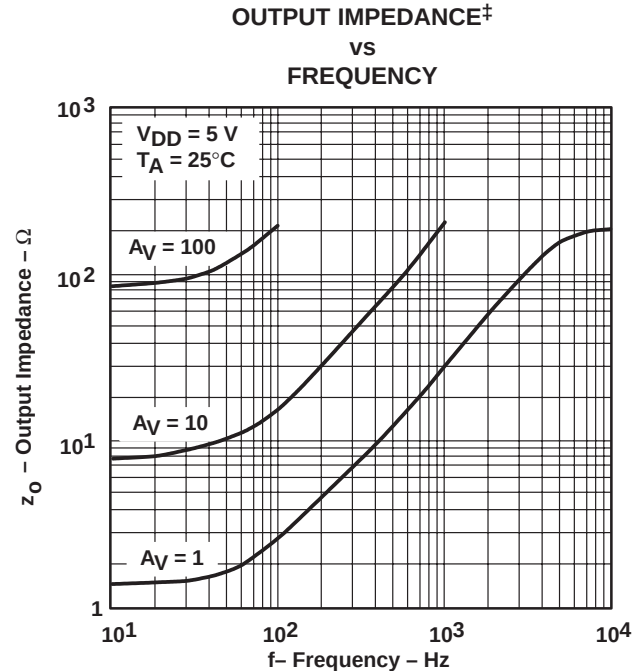


Figure 27

† Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.

‡ For all curves where $V_{DD} = 5\text{ V}$, all loads are referenced to 2.5 V. For all curves where $V_{DD} = 3\text{ V}$, all loads are referenced to 1.5 V.

TYPICAL CHARACTERISTICS

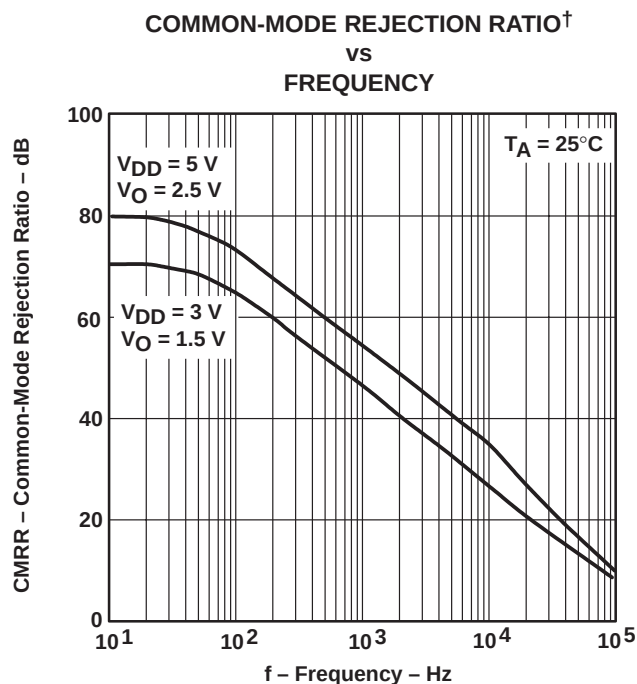


Figure 28

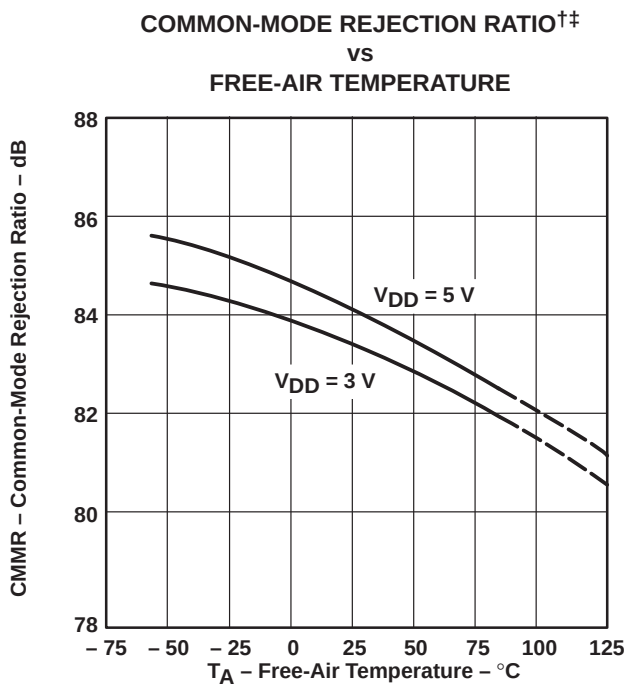


Figure 29

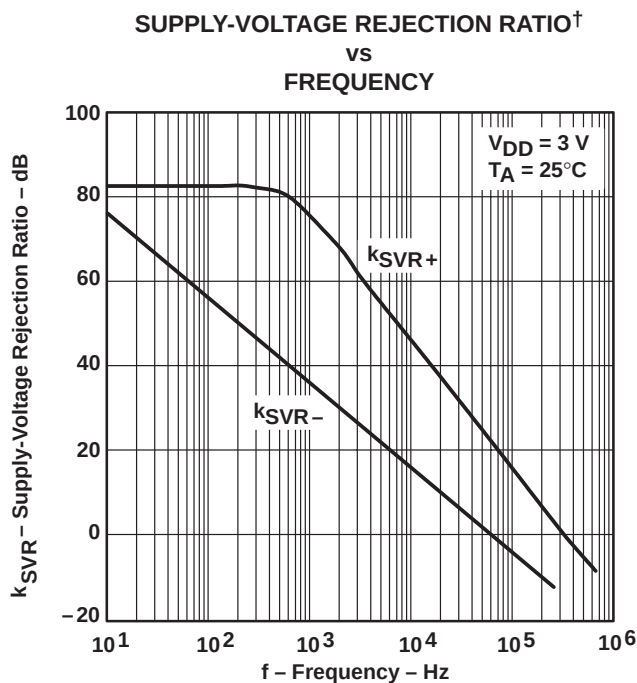


Figure 30

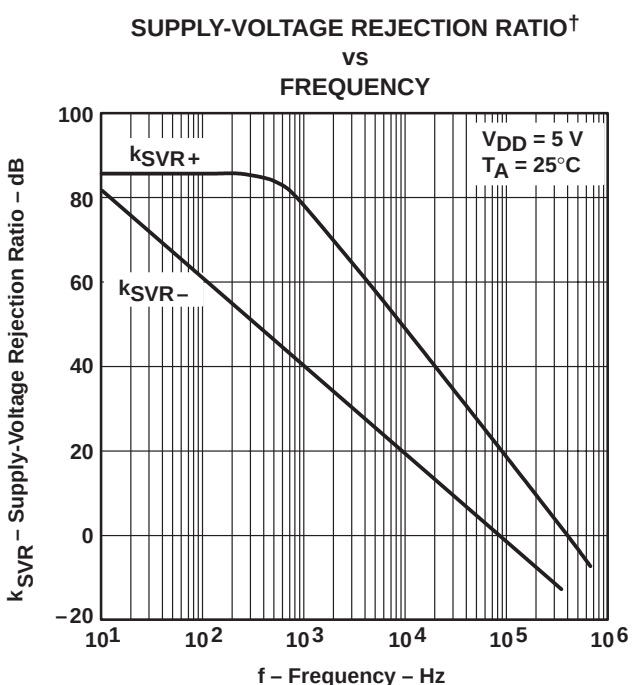


Figure 31

[†] For all curves where $V_{DD} = 5\text{ V}$, all loads are referenced to 2.5 V. For all curves where $V_{DD} = 3\text{ V}$, all loads are referenced to 1.5 V.

[‡] Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.

TYPICAL CHARACTERISTICS

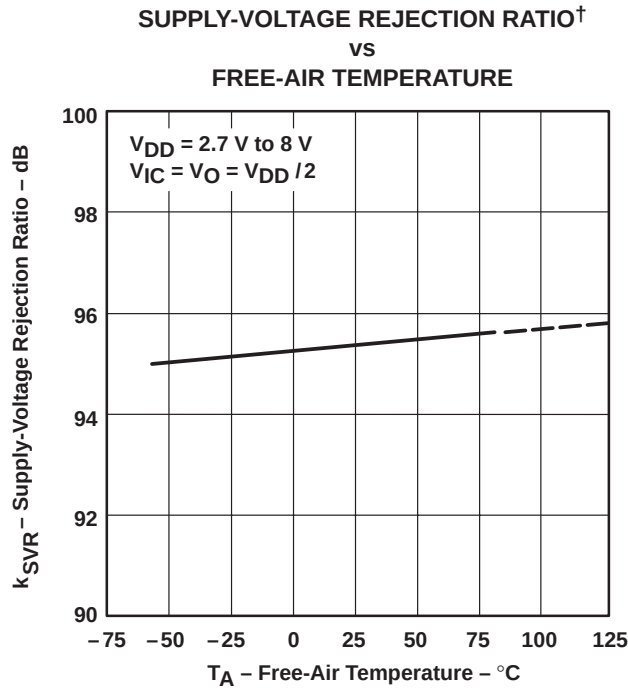


Figure 32

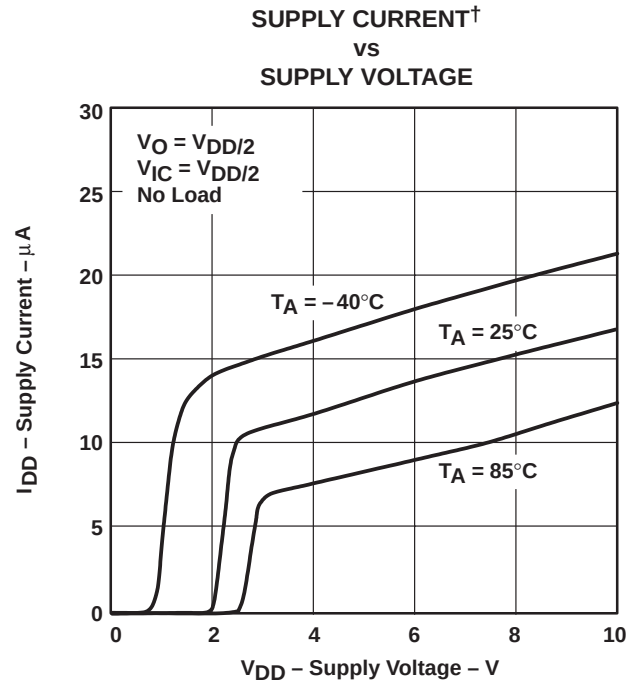


Figure 33

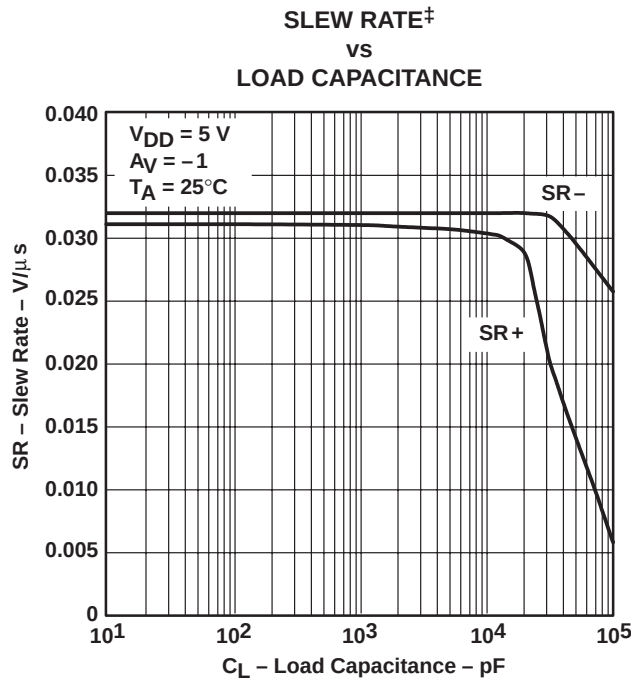


Figure 34

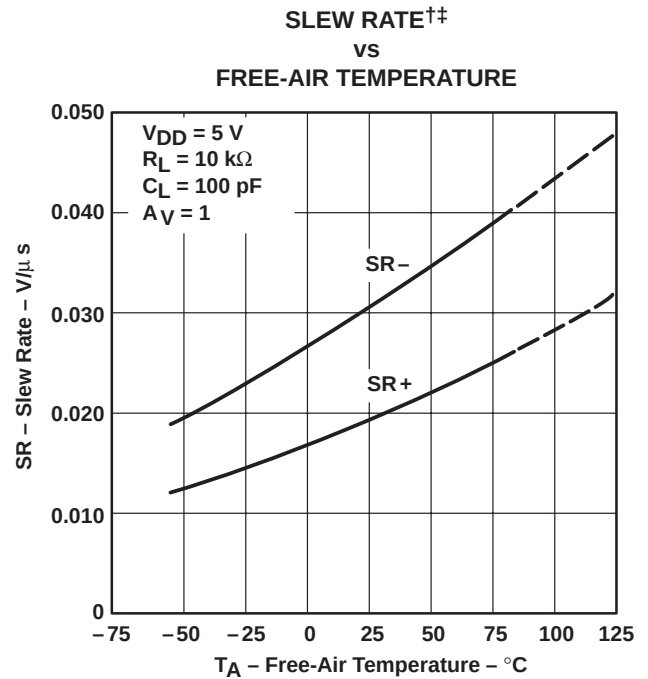


Figure 35

[†] Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.

[‡] For all curves where $V_{DD} = 5 \text{ V}$, all loads are referenced to 2.5 V. For all curves where $V_{DD} = 3 \text{ V}$, all loads are referenced to 1.5 V.

TYPICAL CHARACTERISTICS

INVERTING LARGE-SIGNAL PULSE
RESPONSE†

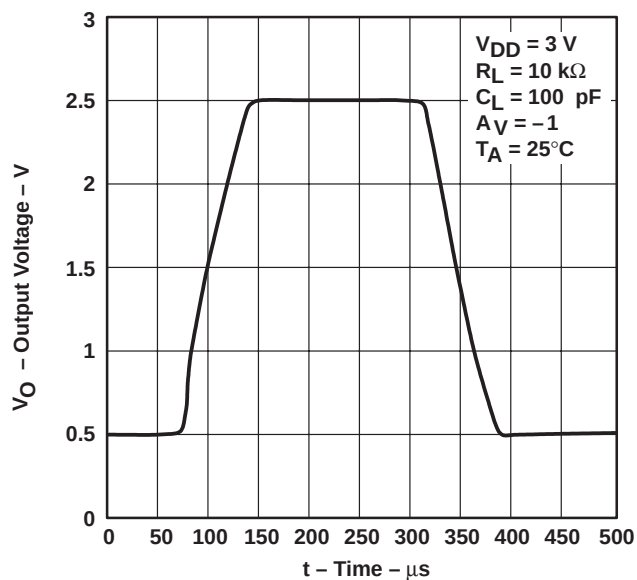


Figure 36

INVERTING LARGE-SIGNAL PULSE
RESPONSE†

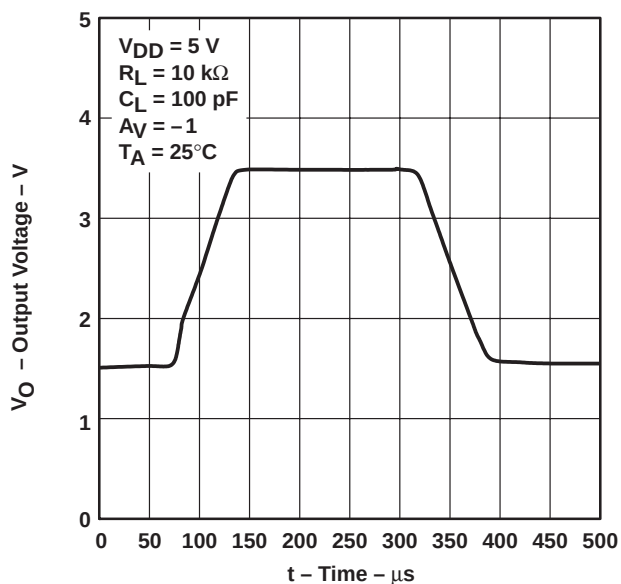


Figure 37

VOLTAGE-FOLLOWER LARGE-SIGNAL
PULSE RESPONSE†

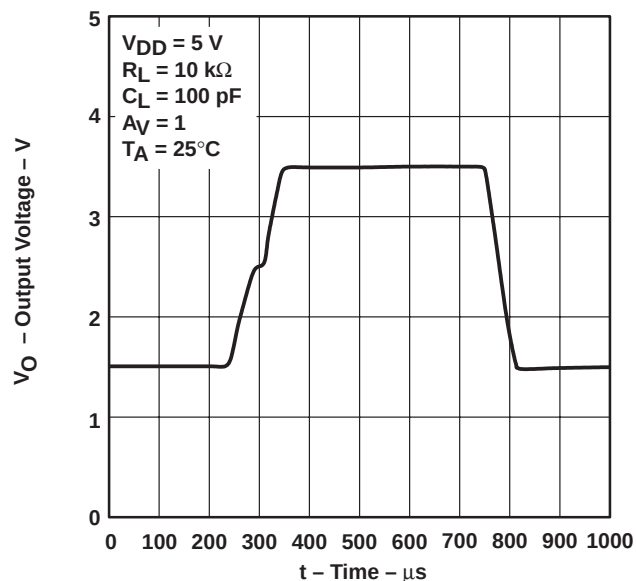


Figure 38

VOLTAGE-FOLLOWER LARGE-SIGNAL
PULSE RESPONSE†

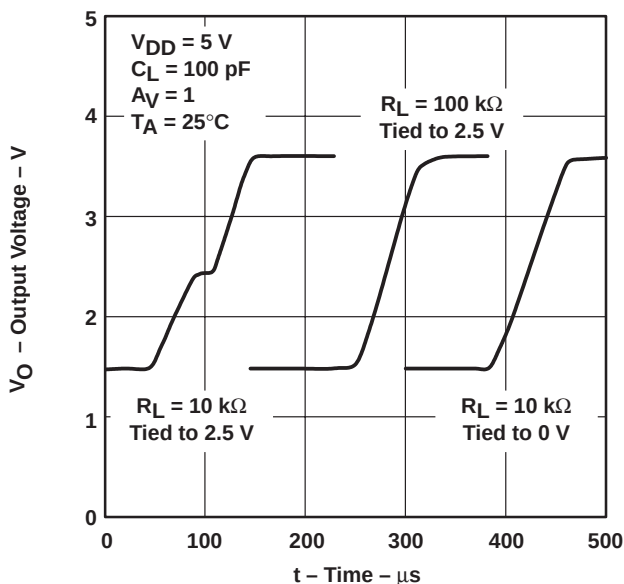


Figure 39

† For all curves where $V_{DD} = 5\text{ V}$, all loads are referenced to 2.5 V. For all curves where $V_{DD} = 3\text{ V}$, all loads are referenced to 1.5 V.

TYPICAL CHARACTERISTICS

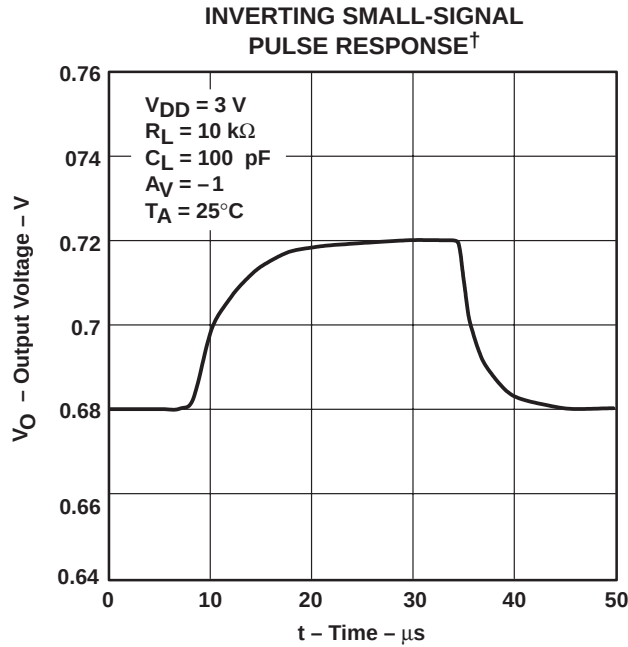


Figure 40

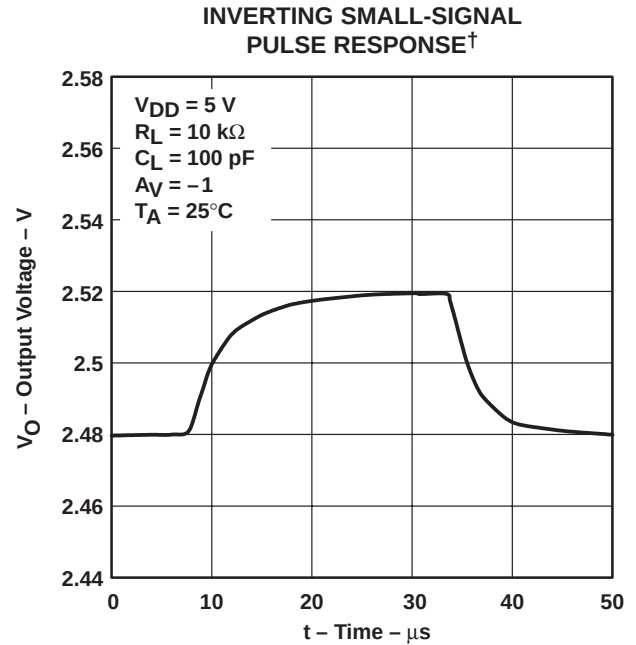


Figure 41

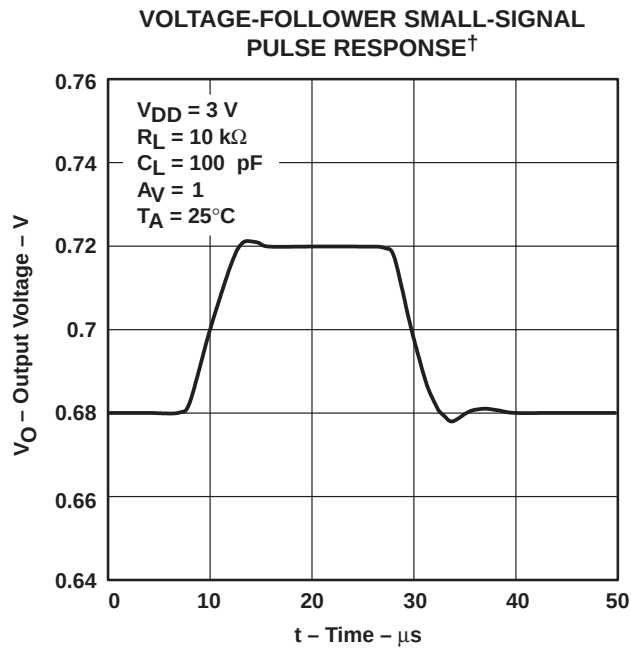


Figure 42

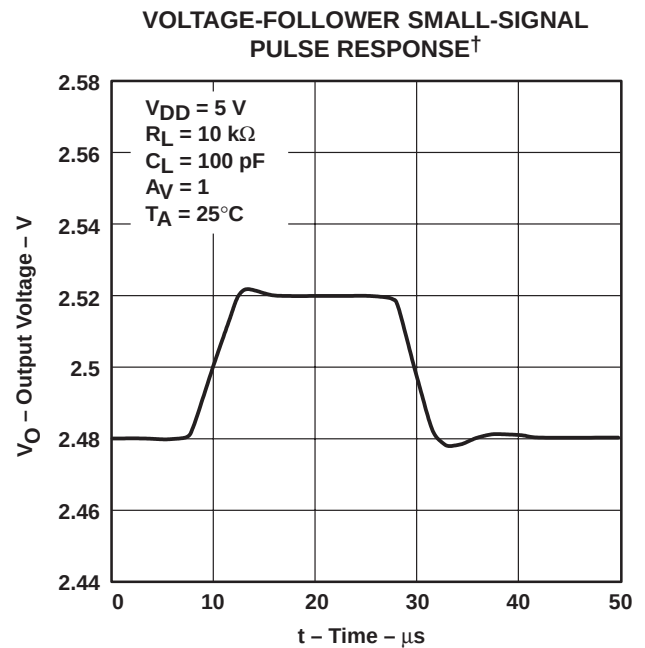


Figure 43

† For all curves where $V_{DD} = 5\text{ V}$, all loads are referenced to 2.5 V. For all curves where $V_{DD} = 3\text{ V}$, all loads are referenced to 1.5 V.

TYPICAL CHARACTERISTICS

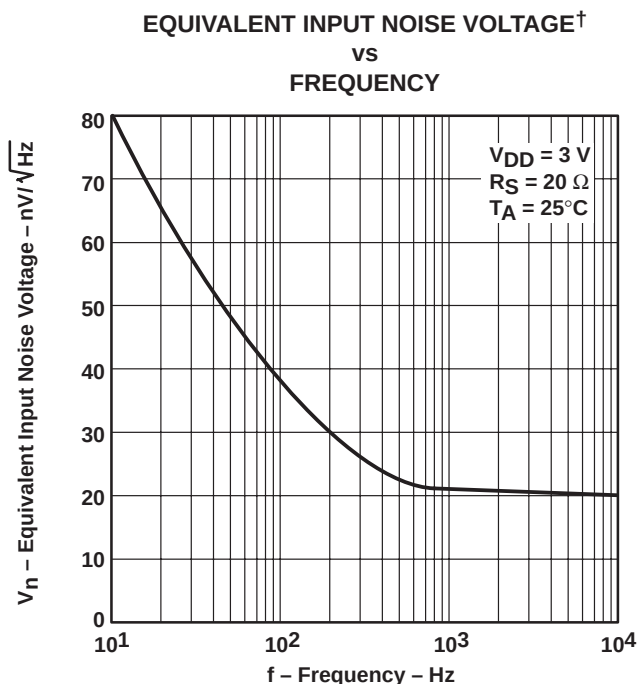


Figure 44

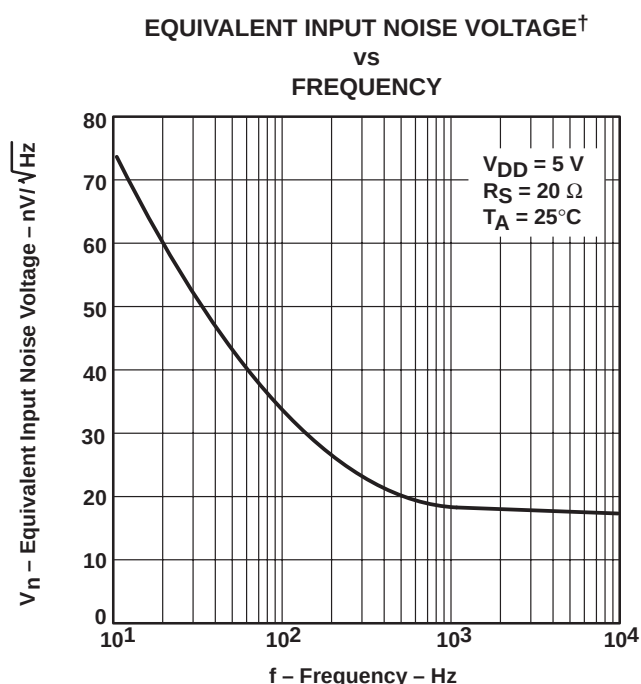


Figure 45

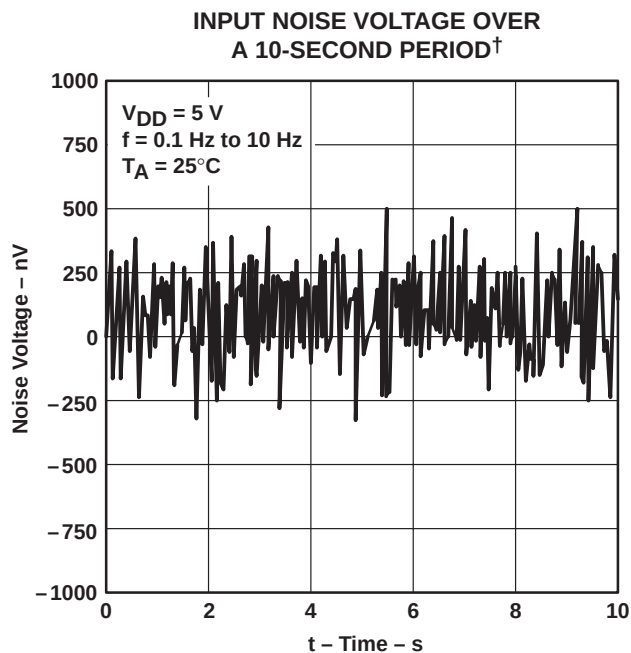


Figure 46

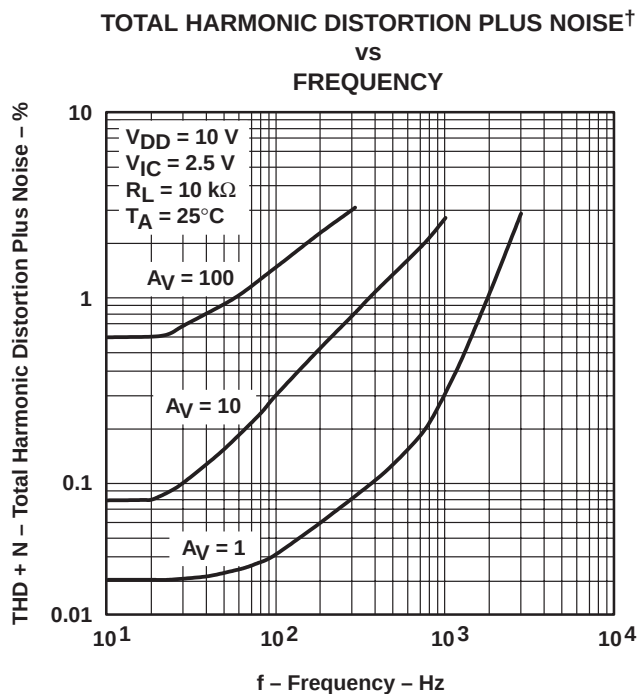


Figure 47

[†] For all curves where $V_{DD} = 5\text{ V}$, all loads are referenced to 2.5 V . For all curves where $V_{DD} = 3\text{ V}$, all loads are referenced to 1.5 V .

TYPICAL CHARACTERISTICS

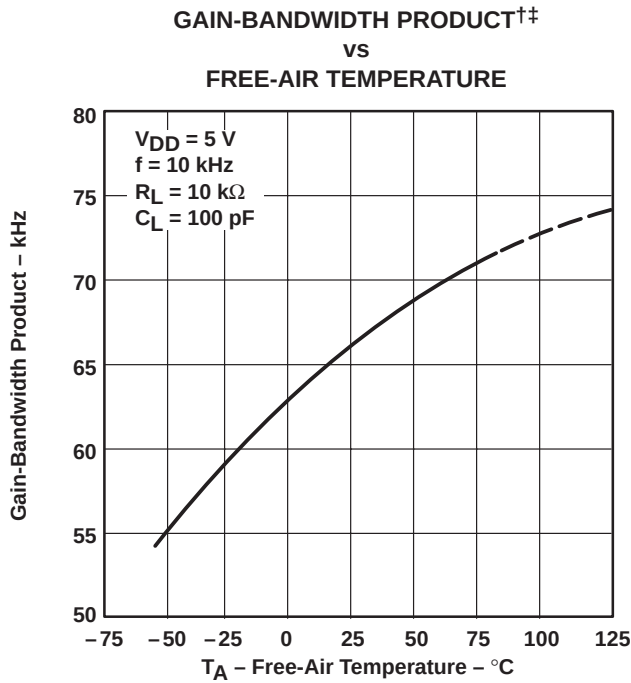


Figure 48

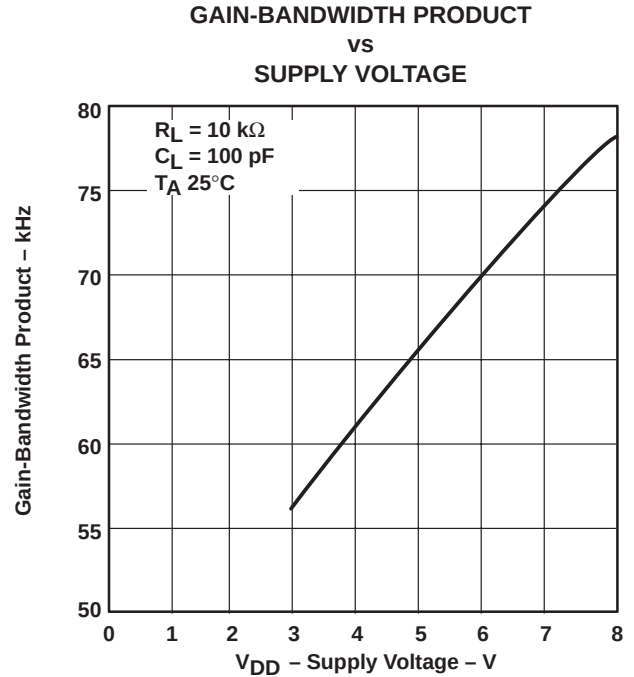


Figure 49

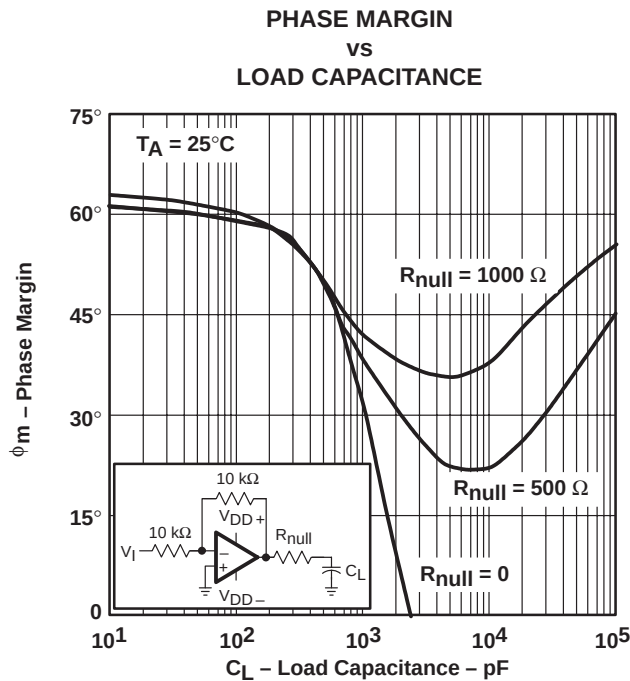


Figure 50

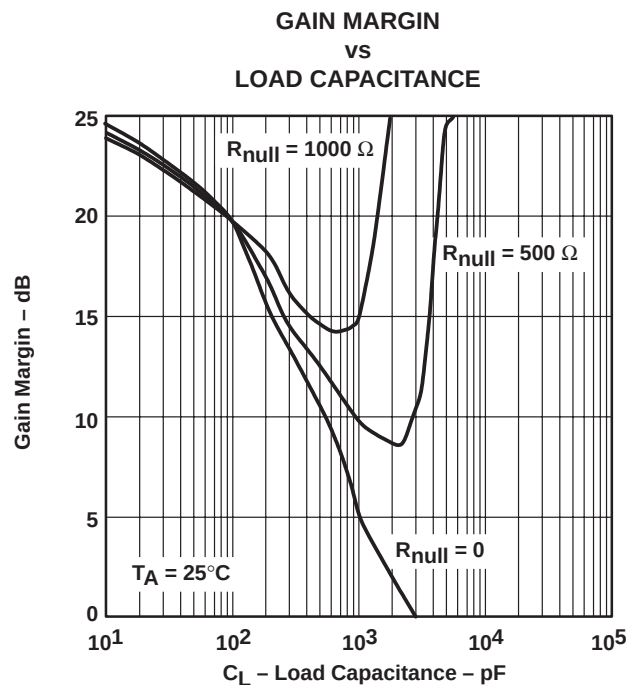


Figure 51

† Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.

‡ For all curves where $V_{DD} = 5\text{ V}$, all loads are referenced to 2.5 V. For all curves where $V_{DD} = 3\text{ V}$, all loads are referenced to 1.5 V.

TYPICAL CHARACTERISTICS

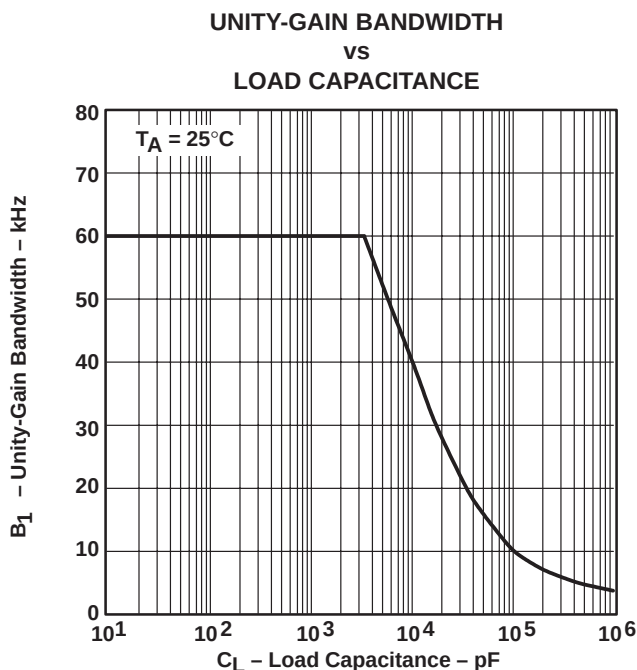


Figure 52

APPLICATION INFORMATION

driving large capacitive loads

The TLV2711 is designed to drive larger capacitive loads than most CMOS operational amplifiers. Figure 50 and Figure 51 illustrate its ability to drive loads up to 600 pF while maintaining good gain and phase margins ($R_{null} = 0$).

A smaller series resistor (R_{null}) at the output of the device (see Figure 53) improves the gain and phase margins when driving large capacitive loads. Figure 50 and Figure 51 show the effects of adding series resistances of 500 Ω and 1000 Ω . The addition of this series resistor has two effects: the first is that it adds a zero to the transfer function and the second is that it reduces the frequency of the pole associated with the output load in the transfer function.

The zero introduced to the transfer function is equal to the series resistance times the load capacitance. To calculate the improvement in phase margin, equation 1 can be used.

$$\Delta\phi_{m1} = \tan^{-1} (2 \times \pi \times \text{UGBW} \times R_{null} \times C_L) \quad (1)$$

where :

$\Delta\phi_{m1}$ = improvement in phase margin

UGBW = unity-gain bandwidth frequency

R_{null} = output series resistance

C_L = load capacitance

APPLICATION INFORMATION

driving large capacitive loads (continued)

The unity-gain bandwidth (UGBW) frequency decreases as the capacitive load increases (see Figure 52). To use equation 1, UGBW must be approximated from Figure 52.

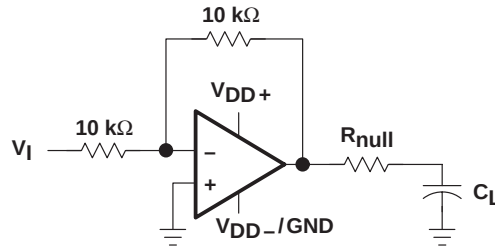


Figure 53. Series-Resistance Circuit

driving heavy dc loads

The TLV2711 is designed to provide better sinking and sourcing output currents than earlier CMOS rail-to-rail output devices. This device is specified to sink 500 μA and source 250 μA at $V_{DD} = 3\text{ V}$ and $V_{DD} = 5\text{ V}$ at a maximum quiescent I_{DD} of 25 μA . This provides a greater than 90% power efficiency.

When driving heavy dc loads, such as 10 k Ω , the positive edge under slewing conditions can experience some distortion. This condition can be seen in Figure 38. This condition is affected by three factors.

- Where the load is referenced. When the load is referenced to either rail, this condition does not occur. The distortion occurs only when the output signal swings through the point where the load is referenced. Figure 39 illustrates two 10-k Ω load conditions. The first load condition shows the distortion seen for a 10-k Ω load tied to 2.5 V. The third load condition shows no distortion for a 10-k Ω load tied to 0 V.
- Load resistance. As the load resistance increases, the distortion seen on the output decreases. Figure 39 illustrates the difference seen on the output for a 10-k Ω load and a 100-k Ω load with both tied to 2.5 V.
- Input signal edge rate. Faster input edge rates for a step input result in more distortion than with slower input edge rates.

TLV2711, TLV2711Y

Advanced LinCMOS™ RAIL-TO-RAIL

MICROPOWER SINGLE OPERATIONAL AMPLIFIERS

SLOS196 – AUGUST 1997

APPLICATION INFORMATION

macromodel information

Macromodel information provided was derived using Microsim *Parts*™, the model generation software used with Microsim *PSpice*™. The Boyle macromodel (see Note 6) and subcircuit in Figure 54 are generated using the TLV2711 typical electrical and operating characteristics at $T_A = 25^\circ\text{C}$. Using this information, output simulations of the following key parameters can be generated to a tolerance of 20% (in most cases):

- Maximum positive output voltage swing
- Maximum negative output voltage swing
- Slew rate
- Quiescent power dissipation
- Input bias current
- Open-loop voltage amplification
- Unity-gain frequency
- Common-mode rejection ratio
- Phase margin
- DC output resistance
- AC output resistance
- Short-circuit output current limit

NOTE 6: G. R. Boyle, B. M. Cohn, D. O. Pederson, and J. E. Solomon, "Macromodeling of Integrated Circuit Operational Amplifiers", *IEEE Journal of Solid-State Circuits*, SC-9, 353 (1974).

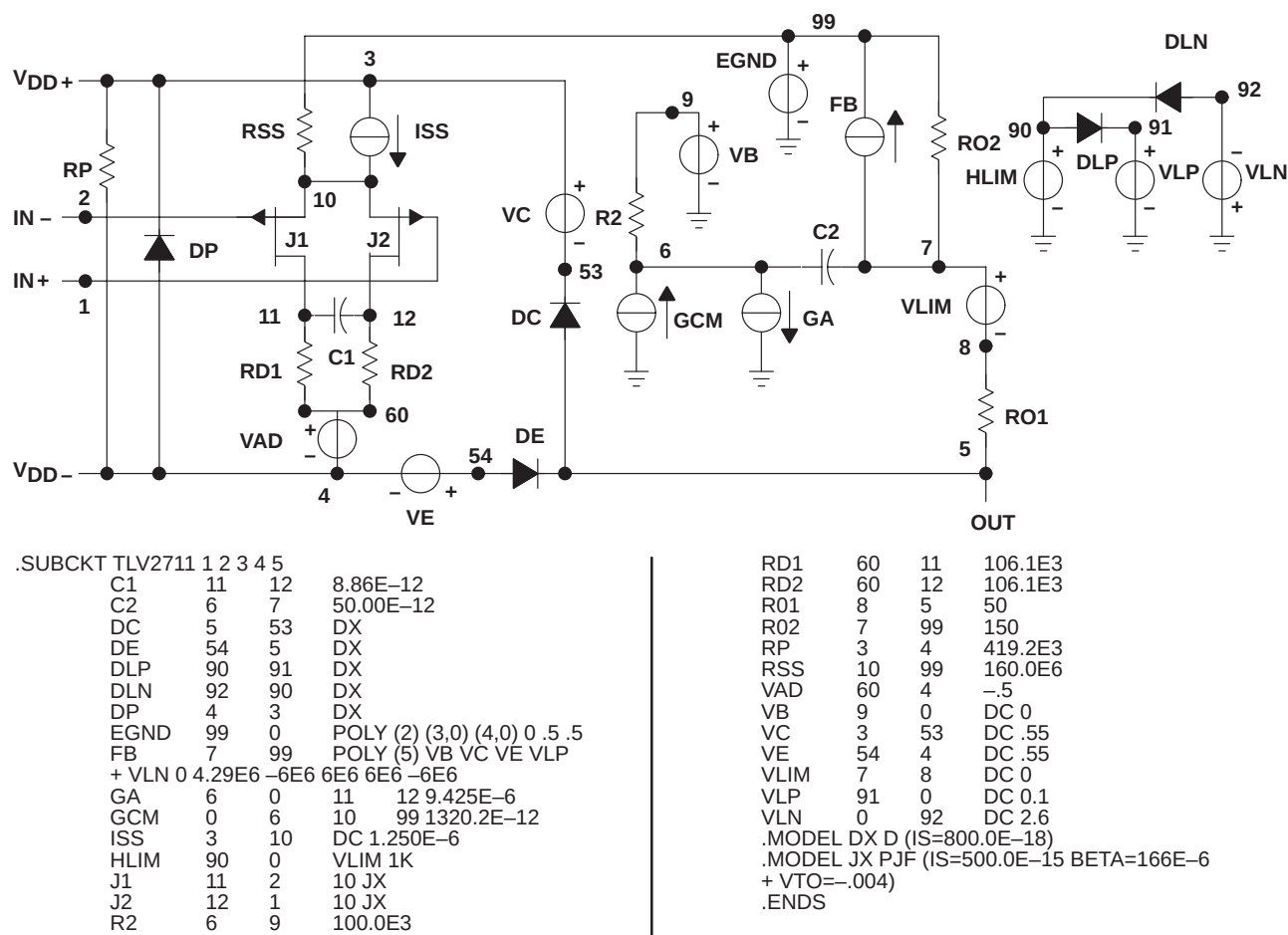


Figure 54. Boyle Macromodel and Subcircuit

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Macromodels, simulation models, or other models provided by TI, directly or indirectly, are not warranted by TI as fully representing all of the specification and operating characteristics of the semiconductor product to which the model relates.

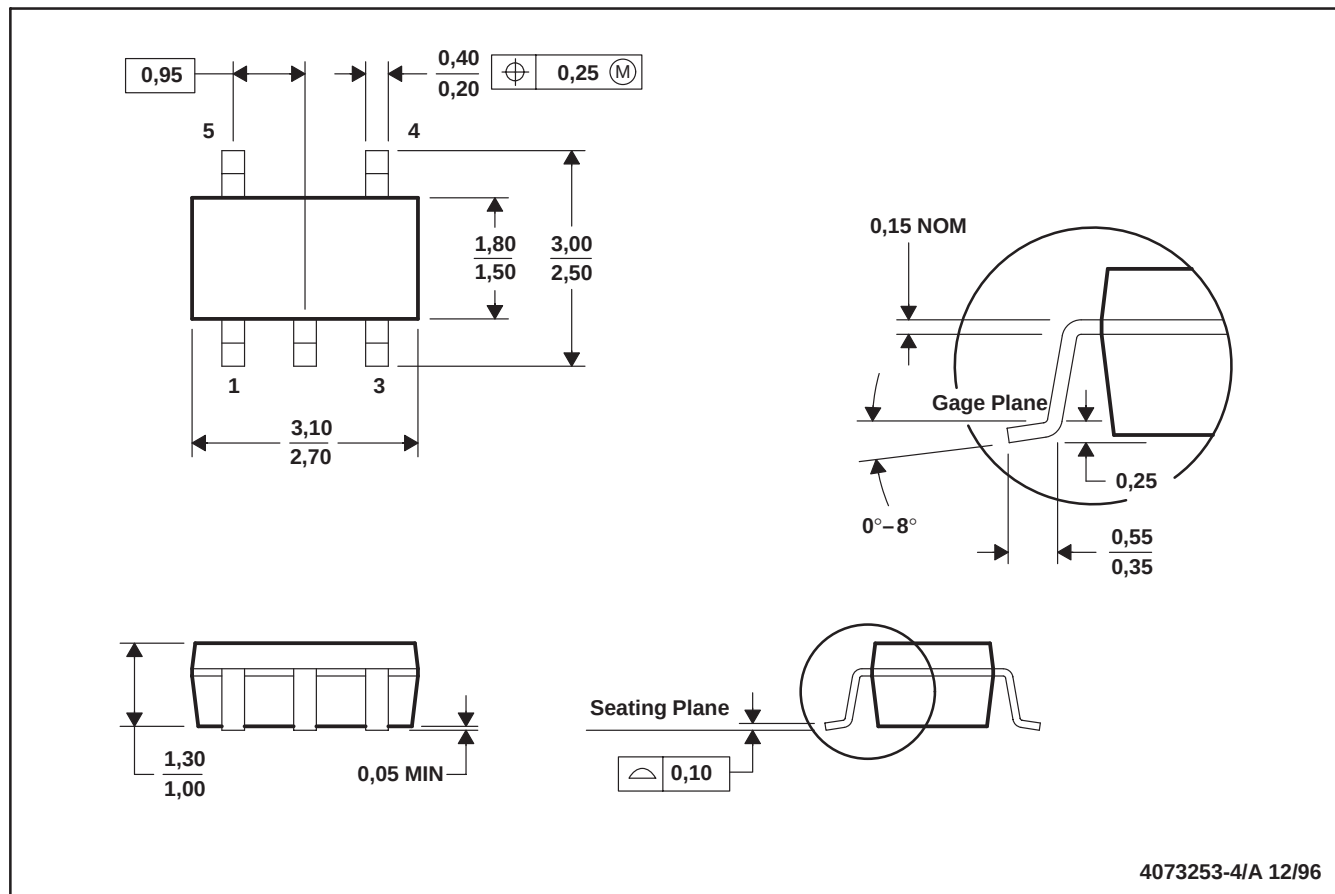


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MECHANICAL INFORMATION

DBV (R-PDSO-G5)

PLASTIC SMALL-OUTLINE PACKAGE



- NOTES:
- A. All linear dimensions are in millimeters.
 - B. This drawing is subject to change without notice.
 - C. Body dimensions include mold flash or protrusion.

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